RTS RIM Testing Services		d Compatibility RF Emission rry® Smartphone model RI		Page 1(216)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	CW

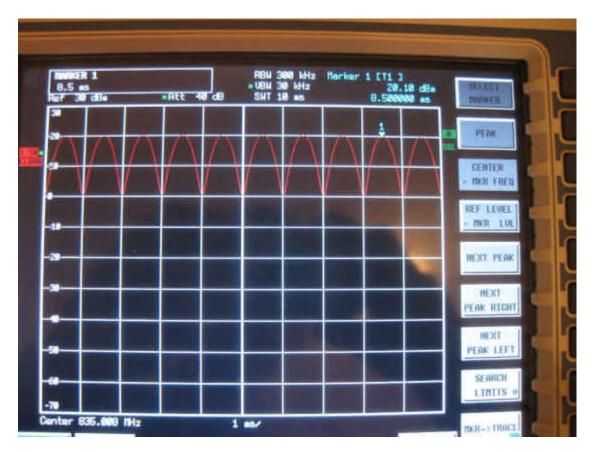
Annex A: Measurement data and plots

A.1 Spectrum analyser plots: CW, 80%AM, GSM and CDMA signals



0 Hz Span CW Plot (835MHz)

RTS RIM Testing Services		I Compatibility RF Emissior rry® Smartphone model RI		Page 2(216)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70CW	



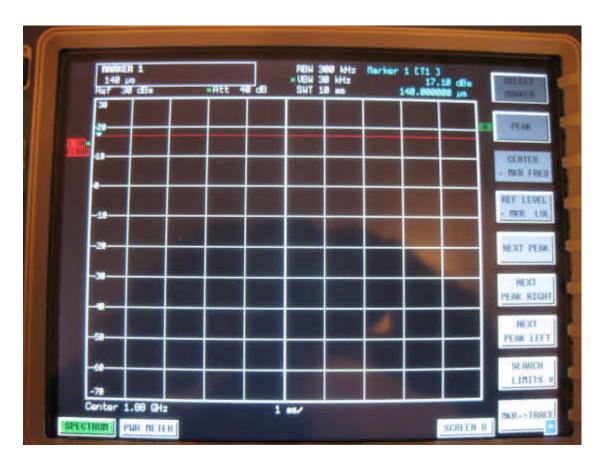
0 Hz Span 80% AM Plot (835MHz)

RTS RIM Testing Services		d Compatibility RF Emission		3(216)
Author Data	Dates of Test	Report No	FCC ID	-
Daoud Attavi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW700	\mathbf{cw}



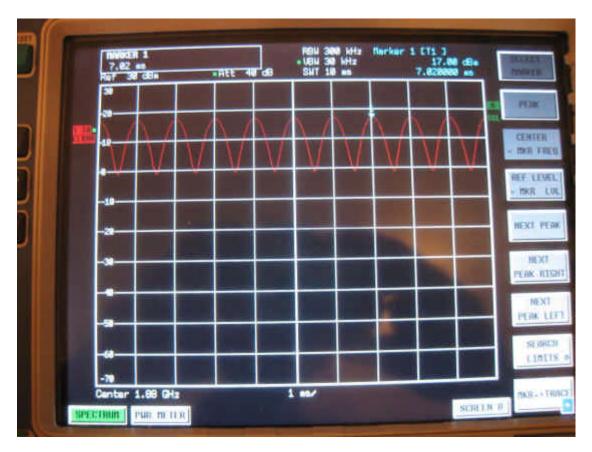
0 Hz Span GSM (835MHz)

RTS RIM Testing Services		I Compatibility RF Emission		Page 4(216)
Author Data Daoud Attayi	Dates of Test Report No FCC ID Aug 26, Sep 26-27, 2008 RTS-1191-0809-30 Rev 1 L6ARBW70CW		'VX /	



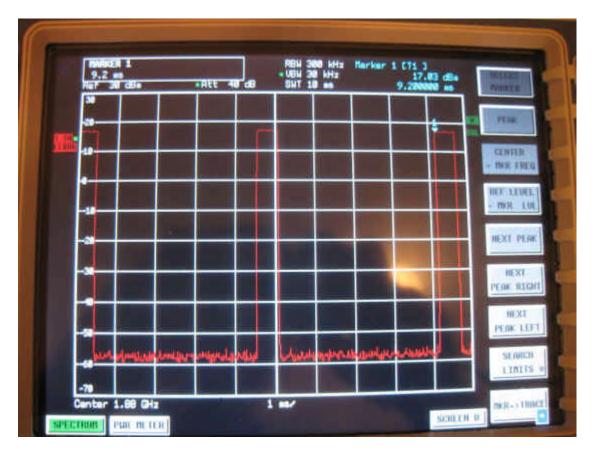
0~Hz~Span~CW~Plot~(1880MHz)

RTS RIM Testing Services		I Compatibility RF Emissior rry® Smartphone model RI		Page 5(216)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70CW	



0 Hz Span 80% AM Plot (1880MHz)

RTS RIM Testing Services		I Compatibility RF Emission rry® Smartphone model RI		Page 6(216)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70CW	



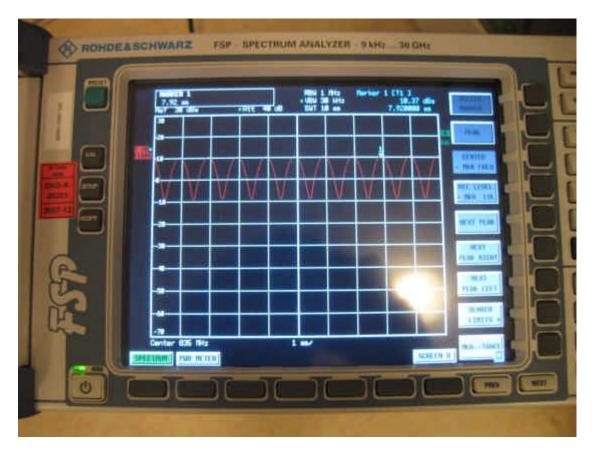
0 Hz Span GSM (1880MHz)

RTS RIM Testing Services		I Compatibility RF Emissior rry® Smartphone model RI		Page 7(216)
Author Data	Dates of Test	Report No	FCC ID	-
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70CW	



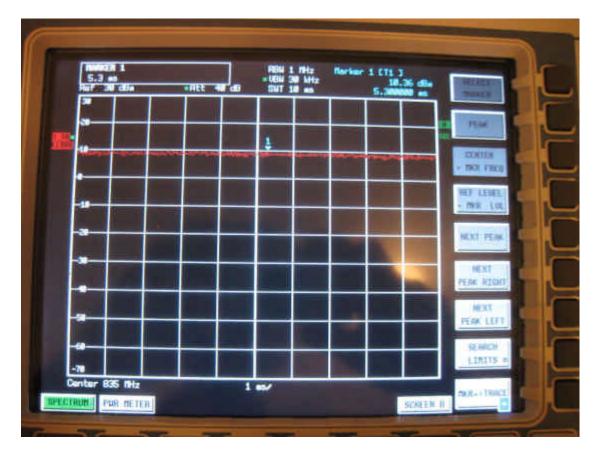
0 Hz Span CW Plot (835MHz)

RTS RIM Testing Services		I Compatibility RF Emissior rry® Smartphone model RE		Page 8(216)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	CW



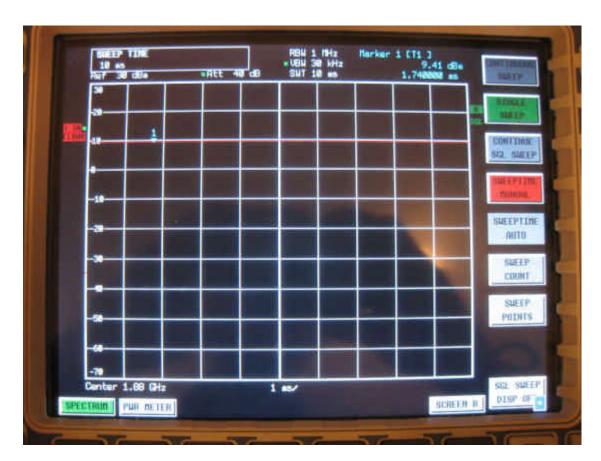
0 Hz Span 80% AM Plot (835MHz)

RTS RIM Testing Services		I Compatibility RF Emissior rry® Smartphone model RE		Page 9(216)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	CW



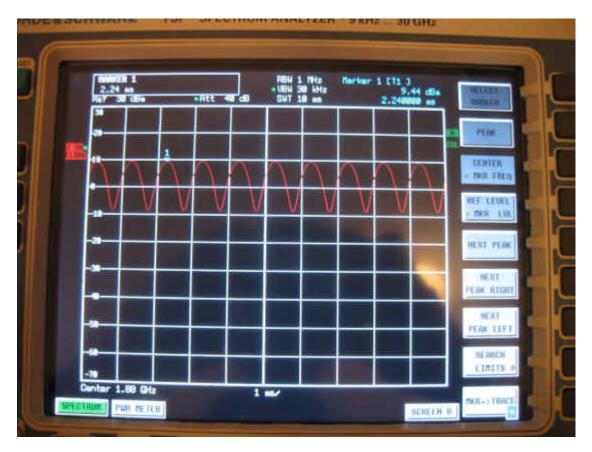
0 Hz Span CDMA (835MHz)

RTS RIM Testing Services		I Compatibility RF Emissior rry® Smartphone model RI		Page 10(216)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70CW	



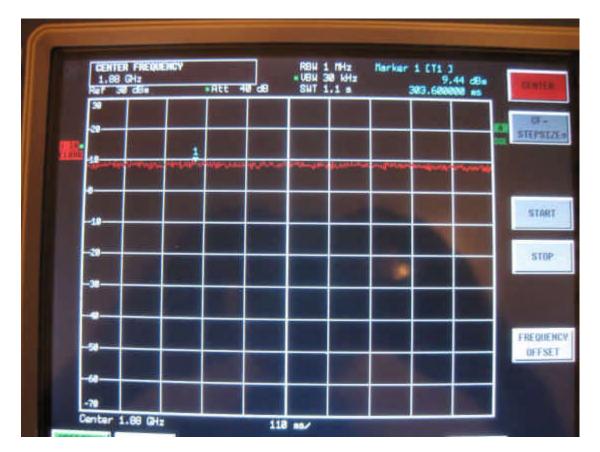
0~Hz~Span~CW~Plot~(1880MHz)

RTS RIM Testing Services		I Compatibility RF Emissior rry® Smartphone model RI		Page 11(216)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70CW	



0 Hz Span 80% AM Plot (1880MHz)

RTS RIM Testing Services	_	I Compatibility RF Emission		Page 12(216)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70CW	



0 Hz Span CDMA (1880MHz)

RTS RIM Testing Services		d Compatibility RF Emissio rry® Smartphone model R		Page 13(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW700	\mathbf{cw}

A.2 Dipole validation and probe modulation factor plots

RTS RIM Testing Services		d Compatibility RF Emission		Page 14(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW700	cw

Date/Time: 26/08/2008 10:30:21 AM

Test Laboratory: RTS

File Name: HAC_E_Dipole_CW835_20.00dBm.da4

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: Not Specified

Program Name: HAC RF E Dipole

Communication System: CW; Frequency: 835 MHz; Duty Cycle: 1:1 Medium parameters used: s = 0 mho/m, $e_r = 1$; density = 1000 kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: ER3DV6 SN2285; ConvF(1, 1, 1); Calibrated: 07/03/2008
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 05/03/2008
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x37x1):

Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 110.4 V/m; Power Drift = -0.029 dB

Maximum value of Total (measured) = 146.7 V/m

RTS RIM Testing Services		d Compatibility RF Emission rry® Smartphone model RI		Page 15(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	CW

(41x361x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 147.2 V/m

Probe Modulation Factor = 1.00

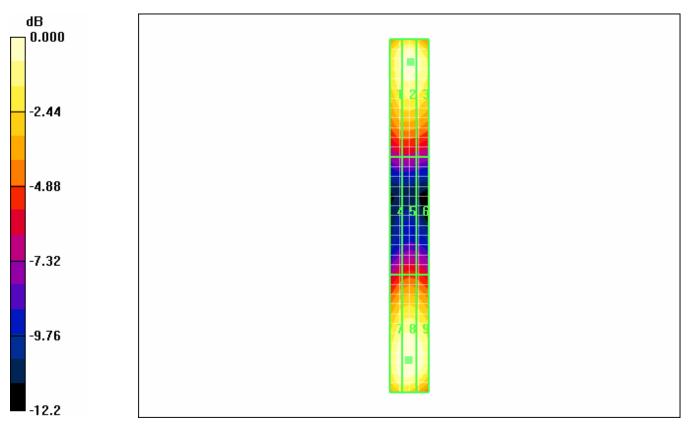
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 110.4 V/m; Power Drift = -0.029 dB

Peak E-field in V/m

Grid 1	Grid 2	Grid 3
139.0	143.6	140.7
\mathbf{M}	\mathbf{M}	\mathbf{M}
4	4	4
Grid 4	Grid 5	Grid 6
78.9	81.2	79.8
M	M	\mathbf{M}
4	4	4
Grid 7	Grid 8	Grid 9
144.9	147.2	145.2
\mathbf{M}	\mathbf{M}	M
4	4	4

RTS RIM Testing Services		d Compatibility RF Emission rry® Smartphone model RI		Page 16(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008 RTS-1191-0809-30 Rev 1 L6ARBW70C			CW



0 dB = 147.2V/m

RTS RIM Testing Services		l Compatibility RF Emissio rry® Smartphone model R		Page 17(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	cw

Date/Time: 26/09/2008 3:00:16 PM

Test Laboratory: RTS

File Name: HAC_E_Dipole_CW835_09_26_08.da4

DUT: HAC-Dipole 835 MHz; Type: D835 V3; Serial: Not Specified

Program Name: HAC RF E Dipole

Communication System: CW; Frequency: 835 MHz; Duty Cycle: 1:1 Medium parameters used: s = 0 mho/m, $e_r = 1$; density = 1000 kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: ER3DV6 SN2285; ConvF(1, 1, 1); Calibrated: 07/03/2008
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 05/03/2008
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x37x1):

Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 111.5 V/m; Power Drift = -0.138 dB

Maximum value of Total (measured) = 148.9 V/m

RTS RIM Testing Services		d Compatibility RF Emissio rry® Smartphone model R		Page 18(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW700	\mathbf{cw}

(41x361x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 149.5 V/m

Probe Modulation Factor = 1.00

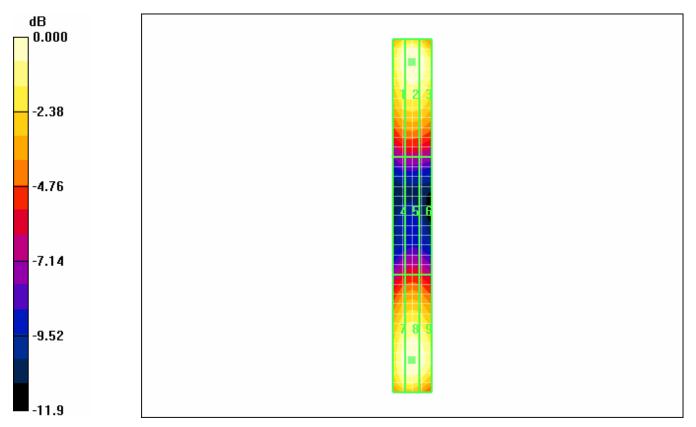
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 111.5 V/m; Power Drift = -0.138 dB

Peak E-field in V/m

Grid 1	Grid 2	Grid 3
146.0	149.5	146.7
\mathbf{M}	M	M
4	4	4
Grid 4	Grid 5	Grid 6
77.3	79.2	77.5
M	M	M
4	4	4
Grid 7	Grid 8	Grid 9
144.6	148.2	145.0
\mathbf{M}	\mathbf{M}	M
4	4	4

RTS RIM Testing Services		d Compatibility RF Emission rry® Smartphone model RI		Page 19(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008 RTS-1191-0809-30 Rev 1 L6ARBW70C			CW



0 dB = 149.5 V/m

RTS RIM Testing Services		d Compatibility RF Emission rry® Smartphone model RI		Page 20(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	CW

Date/Time: 26/09/2008 2:26:11 PM

Test Laboratory: RTS

File Name: HAC_E_Dipole_CW835_PMF_GSM.da4

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: Not Specified

Program Name: HAC RF E Dipole

Communication System: CW; Frequency: 835 MHz; Duty Cycle: 1:1 Medium parameters used: s = 0 mho/m, $e_r = 1$; density = 1000 kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: ER3DV6 SN2285; ConvF(1, 1, 1); Calibrated: 07/03/2008
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 05/03/2008
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x37x1):

Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 115.1 V/m; Power Drift = -0.023 dB

Maximum value of Total (measured) = 157.1 V/m

RTS RIM Testing Services		d Compatibility RF Emissio rry® Smartphone model R		Page 21(216)
Author Data	ates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW700	$\mathbf{C}\mathbf{W}$

(41x361x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 157.7 V/m

Probe Modulation Factor = 1.00

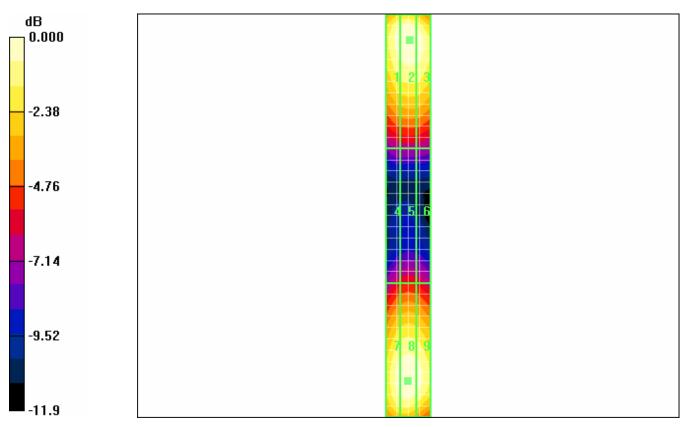
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 115.1 V/m; Power Drift = -0.023 dB

Peak E-field in V/m

Grid 1	Grid 2	Grid 3
154.0	157.7	155.7
M	M	\mathbf{M}
4	4	4
Grid 4	Grid 5	Grid 6
81.4	83.3	81.8
\mathbf{M}	M	M
4	4	4
Grid 7	Grid 8	Grid 9
152.3	156.3	152.8
M	\mathbf{M}	M
4	4	4

RTS RIM Testing Services		d Compatibility RF Emission rry® Smartphone model RI		Page 22(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	CW



0 dB = 157.7V/m

RTS RIM Testing Services	_	l Compatibility RF Emissio rry® Smartphone model R		Page 23(216)
Author Data	ates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	CW

Date/Time: 26/09/2008 2:34:29 PM

Test Laboratory: RTS

File Name: HAC_E_Dipole_AM835_PMF_GSM.da4

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: Not Specified

Program Name: HAC RF E Dipole

Communication System: CW; Frequency: 835 MHz; Duty Cycle: 1:1 Medium parameters used: s = 0 mho/m, $e_r = 1$; density = 1000 kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: ER3DV6 SN2285; ConvF(1, 1, 1); Calibrated: 07/03/2008
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 05/03/2008
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x37x1):

Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 71.6 V/m; Power Drift = 0.109 dB

Maximum value of Total (measured) = 98.3 V/m

RTS RIM Testing Services		d Compatibility RF Emissio rry® Smartphone model R		Page 24(216)
Author Data	ates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW700	\mathbf{cw}

(41x361x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 98.6 V/m

Probe Modulation Factor = 1.00

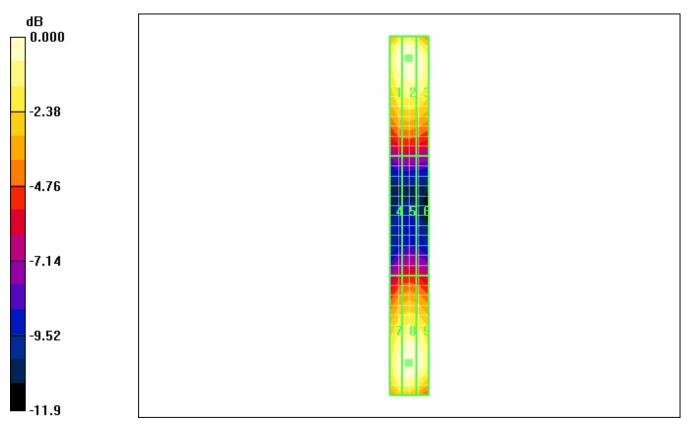
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 71.6 V/m; Power Drift = 0.109 dB

Peak E-field in V/m

Grid 1	Grid 2	Grid 3
97.3 M	98.6 M	97.1 M
4	4	4
Grid 4	Grid 5	Grid 6
51.5	52.6	51.6
M	M	M
4	4	4
Grid 7	Grid 8	Grid 9
94.9	97.1	95.2
M	M	M
4	4	4

RTS RIM Testing Services		d Compatibility RF Emission rry® Smartphone model RI		Page 25(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	CW



0 dB = 98.6 V/m

RTS RIM Testing Services	_	l Compatibility RF Emissio rry® Smartphone model R		Page 26(216)
Author Data	ates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	$\mathbf{c}\mathbf{w}$

Date/Time: 26/09/2008 2:16:10 PM

Test Laboratory: RTS

File Name: HAC_E_Dipole_GSM835.da4

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: Not Specified

Program Name: HAC RF E Dipole

Communication System: GSM 850; Frequency: 835 MHz; Duty Cycle: 1:8.3

Medium parameters used: s = 0 mho/m, $e_r = 1$; density = 1000 kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: ER3DV6 SN2285; ConvF(1, 1, 1); Calibrated: 07/03/2008
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 05/03/2008
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x37x1):

Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 37.8 V/m; Power Drift = 0.079 dB

Maximum value of Total (measured) = 51.2 V/m

RTS RIM Testing Services		l Compatibility RF Emissio rry® Smartphone model RI		Page 27(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	$\mathbf{c}\mathbf{w}$

(41x361x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 51.4 V/m

Probe Modulation Factor = 1.00

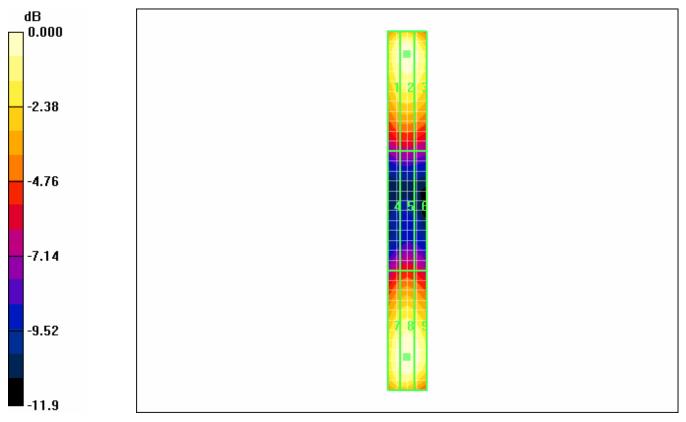
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 37.8 V/m; Power Drift = 0.079 dB

Peak E-field in V/m

Grid 1	Grid 2	Grid 3
48.8	50.1	49.0
M	M	\mathbf{M}
4	4	4
Grid 4	Grid 5	Grid 6
26.6	27.3	26.6
\mathbf{M}	\mathbf{M}	${f M}$
4	4	4
Grid 7	Grid 8	Grid 9
49.8	51.4	50.2
M	M	M
4	4	4

RTS RIM Testing Services		d Compatibility RF Emissio rry® Smartphone model R		Page 28(216)
Author Data	ates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	cw



0 dB = 51.4V/m

RTS RIM Testing Services		I Compatibility RF Emission rry® Smartphone model RI		Page 29(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	CW

Date/Time: 26/09/2008 2:49:40 PM

Test Laboratory: RTS

File Name: HAC_E_Dipole_CW835_PMF_CDMA.da4

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: Not Specified

Program Name: HAC RF E Dipole

Communication System: CW; Frequency: 835 MHz; Duty Cycle: 1:1 Medium parameters used: s = 0 mho/m, $e_r = 1$; density = 1000 kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: ER3DV6 SN2285; ConvF(1, 1, 1); Calibrated: 07/03/2008
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 05/03/2008
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x37x1):

Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 38.4 V/m; Power Drift = 0.108 dB

Maximum value of Total (measured) = 52.3 V/m

RTS RIM Testing Services		I Compatibility RF Emissio rry® Smartphone model RI		Page 30(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	$\mathbf{c}\mathbf{w}$

(41x361x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 52.4 V/m

Probe Modulation Factor = 1.00

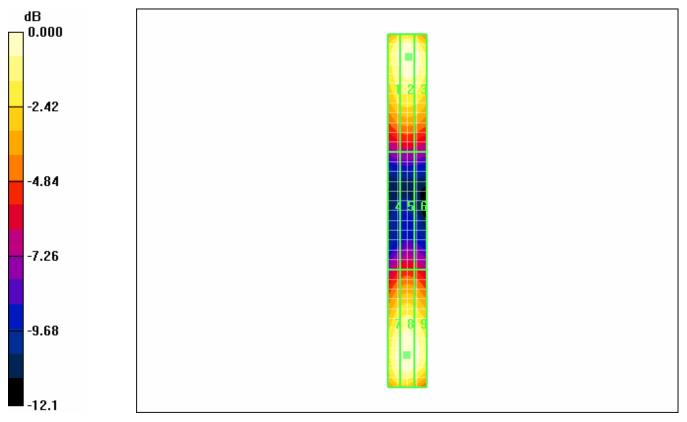
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 38.4 V/m; Power Drift = 0.108 dB

Peak E-field in V/m

Grid 1	Grid 2	Grid 3
50.6	52.3	51.6
M	M	M
4	4	4
Grid 4	Grid 5	Grid 6
27.2	28.0	27.4
M	\mathbf{M}	\mathbf{M}
4	4	4
Grid 7	Grid 8	Grid 9
51.0	52.4	51.2
M	M	M
4	4	4

RTS RIM Testing Services		d Compatibility RF Emission rry® Smartphone model R		Page 31(216)
Author Data	ates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	CW



0 dB = 52.4V/m

RTS RIM Testing Services		I Compatibility RF Emission rry® Smartphone model RI		Page 32(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	CW

Date/Time: 26/09/2008 2:41:20 PM

Test Laboratory: RTS

File Name: HAC_E_Dipole_AM835_PMF_CDMA.da4

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: Not Specified

Program Name: HAC RF E Dipole

Communication System: CW; Frequency: 835 MHz; Duty Cycle: 1:1 Medium para meters used: s = 0 mho/m, $e_r = 1$; density = 1000 kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: ER3DV6 SN2285; ConvF(1, 1, 1); Calibrated: 07/03/2008
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 05/03/2008
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x37x1):

Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 24.4 V/m; Power Drift = 0.011 dB

Maximum value of Total (measured) = 32.8 V/m

RTS RIM Testing Services	_	d Compatibility RF Emissio rry® Smartphone model R		Page 33(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW700	$\mathbf{c}\mathbf{w}$

(41x361x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 32.9 V/m

Probe Modulation Factor = 1.00

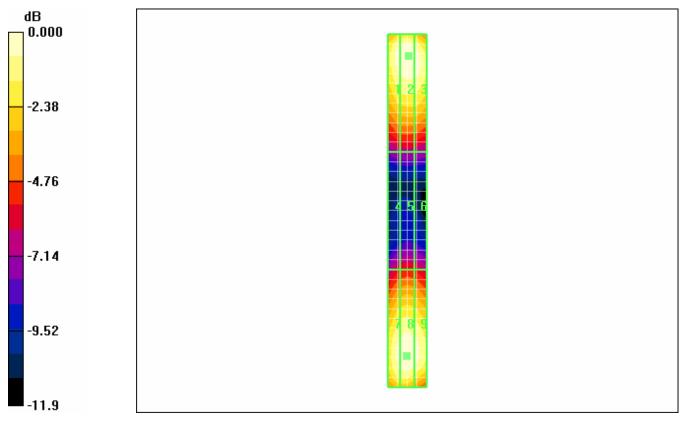
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 24.4 V/m; Power Drift = 0.011 dB

Peak E-field in V/m

Grid 1	Grid 2	Grid 3
32.1	32.9	32.5
M	M	\mathbf{M}
4	4	4
Grid 4	Grid 5	Grid 6
17.1	17.5	17.2
\mathbf{M}	\mathbf{M}	${f M}$
4	4	4
Grid 7	Grid 8	Grid 9
31.7	32.5	31.7
M	M	M
4	4	4

RTS RIM Testing Services		d Compatibility RF Emissio rry® Smartphone model R		Page 34(216)
Author Data	Pates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	CW



0 dB = 32.9V/m

RTS RIM Testing Services		I Compatibility RF Emission rry® Smartphone model RI		Page 35(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	CW

Date/Time: 26/09/2008 3:16:30 PM

Test Laboratory: RTS

File Name: HAC_E_Dipole_CDMA835_R2.da4

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: Not Specified

Program Name: HAC RF E Dipole

Communication System: CW; Frequency: 835 MHz; Duty Cycle: 1:1 Medium parameters used: s = 0 mho/m, $e_r = 1$; density = 1000 kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: ER3DV6 SN2285; ConvF(1, 1, 1); Calibrated: 07/03/2008
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 05/03/2008
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x37x1):

Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 41.3 V/m; Power Drift = -0.106 dB

Maximum value of Total (measured) = 55.2 V/m

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Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	$\mathbf{c}\mathbf{w}$

(41x361x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 55.4 V/m

Probe Modulation Factor = 1.00

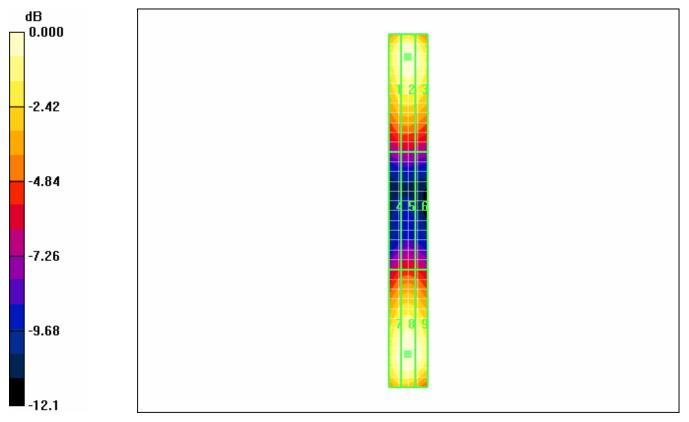
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 41.3 V/m; Power Drift = -0.106 dB

Peak E-field in V/m

Grid 1	Grid 2	Grid 3
53.0	54.4	53.0
M	M	M
4	4	4
Grid 4	Grid 5	Grid 6
29.2	29.4	28.9
M	\mathbf{M}	${f M}$
4	4	4
Grid 7	Grid 8	Grid 9
54.7	55.4	54.3
M	M	M
4	4	4

RTS RIM Testing Services		d Compatibility RF Emission rry® Smartphone model RI		Page 37(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	CW



 $0\ dB = 55.4V/m$

RTS RIM Testing Services		I Compatibility RF Emission rry® Smartphone model RI		Page 38(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	cw

Date/Time: 26/08/2008 10:11:51 AM

Test Laboratory: RTS

File Name: HAC_E_Dipole_CW1880_20.00dBm.da4

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: Not Specified

Program Name: HAC RF E Dipole

Communication System: CW; Frequency: 1880 MHz; Duty Cycle: 1:1 Medium parameters used: s = 0 mho/m, $e_r = 1$; density = 1000 kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: ER3DV6 SN2285; ConvF(1, 1, 1); Calibrated: 07/03/2008
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 05/03/2008
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - measurement distance from the probe sensor center to CD1880 Dipole = 10mm/Hearing Aid Compatibility Test

(5x19x1): Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 118.5 V/m; Power Drift = 0.009 dB

Maximum value of Total (measured) = 117.7 V/m

RTS RIM Testing Services		d Compatibility RF Emissio rry® Smartphone model R		^{Page} 39(216)
Author Data	Pates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW700	\mathbf{cw}

(41x181x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 120.1 V/m

Probe Modulation Factor = 1.00

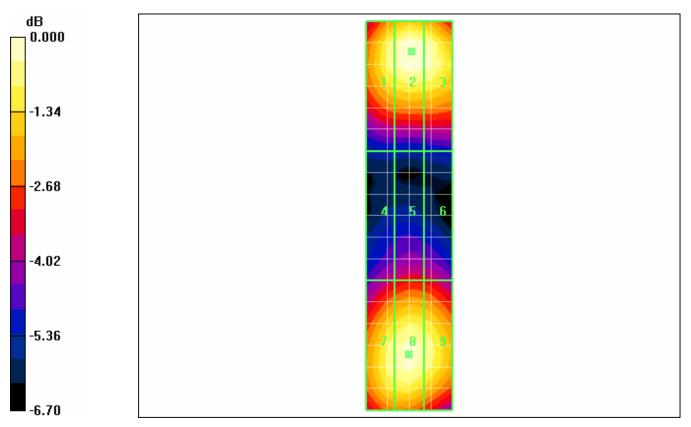
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 118.5 V/m; Power Drift = 0.009 dB

Peak E-field in V/m

Grid 1	Grid 2	Grid 3
115.1	120.1	118.2
\mathbf{M}	M	M
2	2	2
Grid 4	Grid 5	Grid 6
80.1	83.4	82.5
M	M	M
3	3	3
Grid 7	Grid 8	Grid 9
114.0	116.6	113.6
M	\mathbf{M}	M
2	2	2

RTS RIM Testing Services		d Compatibility RF Emission rry® Smartphone model RI		Page 40(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	CW



0 dB = 120.1 V/m

RTS RIM Testing Services		l Compatibility RF Emissio rry® Smartphone model R		Page 41(216)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	cw

Date/Time: 26/09/2008 12:51:51 PM

Test Laboratory: RTS

File Name: HAC_E_Dipole_CW1880_20.00dBm_26_09_08.da4

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: Not Specified

Program Name: HAC RF E Dipole

Communication System: CW; Frequency: 1880 MHz; Duty Cycle: 1:1 Medium parameters used: s = 0 mho/m, $e_r = 1$; density = 1000 kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: ER3DV6 SN2285; ConvF(1, 1, 1); Calibrated: 07/03/2008
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 05/03/2008
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - measurement distance from the probe sensor center to CD1880 Dipole = 10mm/Hearing Aid Compatibility Test

(5x19x1): Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 123.4 V/m; Power Drift = 0.006 dB

Maximum value of Total (measured) = 123.6 V/m

RTS RIM Testing Services		d Compatibility RF Emissio rry® Smartphone model R		Page 42(216)
Author Data	ates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW700	\mathbf{cw}

(41x181x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 125.9 V/m

Probe Modulation Factor = 1.00

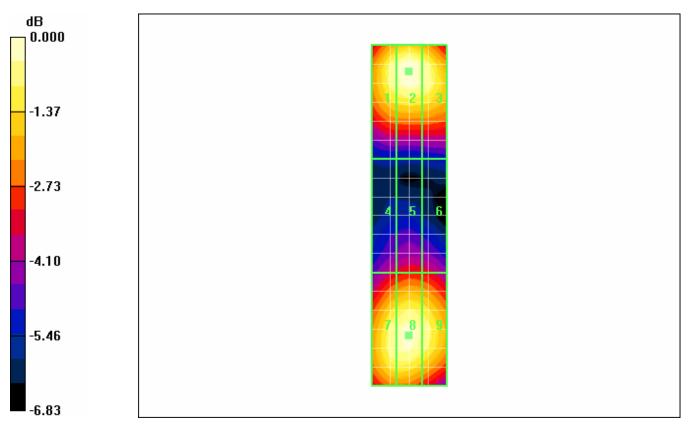
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 123.4 V/m; Power Drift = 0.006 dB

Peak E-field in V/m

Grid 1	Grid 2	Grid 3
122.2	125.9	122.0
\mathbf{M}	M	M
2	2	2
Grid 4	Grid 5	Grid 6
84.7	88.0	86.7
M	M	\mathbf{M}
3	3	3
Grid 7	Grid 8	Grid 9
120.5	122.4	119.0
M	\mathbf{M}	M
2	2	2

RTS RIM Testing Services		d Compatibility RF Emission rry® Smartphone model RI		Page 43(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	CW



0 dB = 125.9V/m

RTS RIM Testing Services	_	d Compatibility RF Emissio rry® Smartphone model R		Page 44(216)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	$\mathbf{c}\mathbf{w}$

Date/Time: 26/09/2008 12:58:06 PM

Test Laboratory: RTS

File Name: HAC_E_Dipole_CW1880_PMF_GSM.da4

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: Not Specified

Program Name: HAC RF E Dipole

Communication System: CW; Frequency: 1880 MHz; Duty Cycle: 1:1 Medium parameters used: s = 0 mho/m, $e_r = 1$; density = 1000 kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: ER3DV6 SN2285; ConvF(1, 1, 1); Calibrated: 07/03/2008
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 05/03/2008
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - measurement distance from the probe sensor center to CD1880 Dipole = 10mm/Hearing Aid Compatibility Test

(5x19x1): Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 89.5 V/m; Power Drift = 0.001 dB

Maximum value of Total (measured) = 89.7 V/m

RTS RIM Testing Services		d Compatibility RF Emissio rry® Smartphone model R		Page 45(216)
Author Data	ates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW700	\mathbf{cw}

(41x181x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 91.3 V/m

Probe Modulation Factor = 1.00

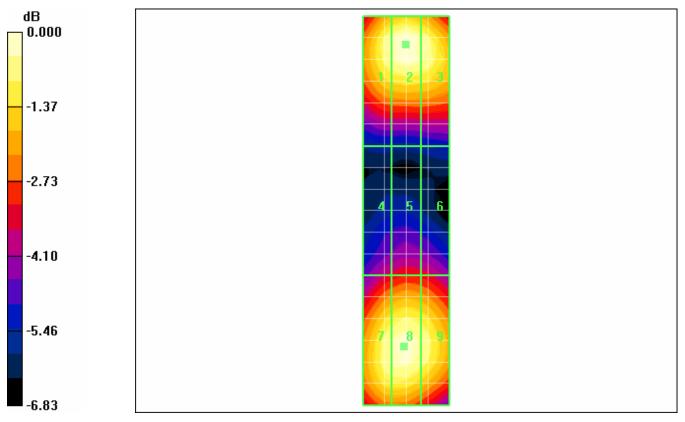
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 89.5 V/m; Power Drift = 0.001 dB

Peak E-field in V/m

Grid 1	Grid 2	Grid 3
88.4	91.3	88.5
\mathbf{M}	M	M
3	3	3
Grid 4	Grid 5	Grid 6
61.5	63.7	62.7
M	M	\mathbf{M}
4	3	4
Grid 7	Grid 8	Grid 9
87.4	88.9	86.1
M	M	M
3	3	3

RTS RIM Testing Services		d Compatibility RF Emissio rry® Smartphone model R		Page 46(216)
Author Data	Pates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	CW



0 dB = 91.3V/m

RTS RIM Testing Services		d Compatibility RF Emission rry® Smartphone model RI		Page 47(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	CW

Date/Time: 26/09/2008 1:12:00 PM

Test Laboratory: RTS

File Name: HAC_E_Dipole_AM_1880_PMF_GSM.da4

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: Not Specified

Program Name: HAC RF E Dipole

Communication System: CW; Frequency: 1880 MHz; Duty Cycle: 1:1 Medium parameters used: s = 0 mho/m, $e_r = 1$; density = 1000 kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: ER3DV6 SN2285; ConvF(1, 1, 1); Calibrated: 07/03/2008
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 05/03/2008
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - measurement distance from the probe sensor center to CD1880 Dipole = 10mm/Hearing Aid Compatibility Test

(5x19x1): Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 56.2 V/m; Power Drift = 0.021 dB

Maximum value of Total (measured) = 56.5 V/m

RTS RIM Testing Services		d Compatibility RF Emissio rry® Smartphone model R		Page 48(216)
Author Data	ates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW700	\mathbf{cw}

(41x181x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 57.5 V/m

Probe Modulation Factor = 1.00

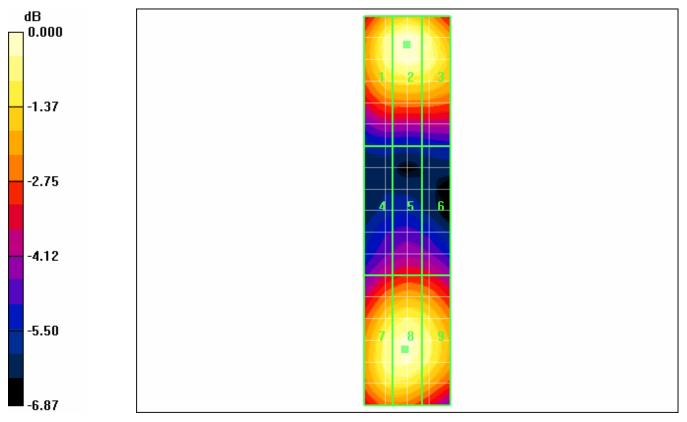
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 56.2 V/m; Power Drift = 0.021 dB

Peak E-field in V/m

Grid 1	Grid 2	Grid 3
55.9	57.5	55.8
M	M	M
4	4	4
Grid 4	Grid 5	Grid 6
38.8	40.2	39.6
M	M	M
4	4	4
Grid 7	Grid 8	Grid 9
54.9	55.8	54.2
M	M	M
4	4	4

RTS RIM Testing Services		d Compatibility RF Emissio rry® Smartphone model R		Page 49(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	CW



0 dB = 57.5 V/m

RTS RIM Testing Services		d Compatibility RF Emission rry® Smartphone model RI		Page 50(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW700	cw

Date/Time: 26/09/2008 1:48:32 PM

Test Laboratory: RTS

File Name: HAC_E_Dipole_GSM1880.da4

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: Not Specified

Program Name: HAC RF E Dipole

Communication System: GSM 1900; Frequency: 1880 MHz; Duty Cycle: 1:8.3

Medium parameters used: s = 0 mho/m, $e_r = 1$; density = 1000 kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: ER3DV6 SN2285; ConvF(1, 1, 1); Calibrated: 07/03/2008
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 05/03/2008
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - measurement distance from the probe sensor center to CD1880 Dipole = 10mm/Hearing Aid Compatibility Test

(5x19x1): Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 32.4 V/m; Power Drift = -0.087 dB

Maximum value of Total (measured) = 31.5 V/m

RTS RIM Testing Services		d Compatibility RF Emissio rry® Smartphone model R		Page 51(216)
Author Data	ates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW700	\mathbf{cw}

(41x181x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 31.7 V/m

Probe Modulation Factor = 1.00

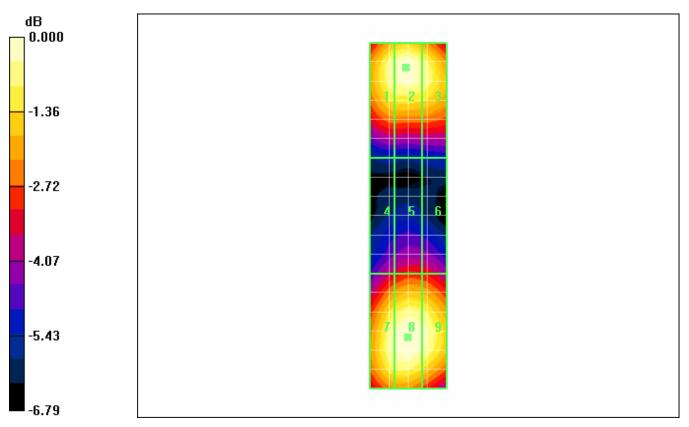
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 32.4 V/m; Power Drift = -0.087 dB

Peak E-field in V/m

Grid 1	Grid 2	Grid 3
30.8	31.6	30.4
M	M	\mathbf{M}
4	4	4
Grid 4	Grid 5	Grid 6
21.4	22.5	22.2
M	M	\mathbf{M}
4	4	4
Grid 7	Grid 8	Grid 9
30.8	31.7	31.0
M	M	M
4	4	4

RTS RIM Testing Services		d Compatibility RF Emission rry® Smartphone model RI		Page 52(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008 RTS-1191-0809-30 Rev 1 L6ARBW700			CW



0 dB = 31.7V/m

RTS RIM Testing Services		d Compatibility RF Emission rry® Smartphone model RI		Page 53(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW700	CW

Date/Time: 26/09/2008 1:03:21 PM

Test Laboratory: RTS

File Name: HAC_E_Dipole_CW1880_PMF_CDMA.da4

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: Not Specified

Program Name: HAC RF E Dipole

Communication System: CW; Frequency: 1880 MHz; Duty Cycle: 1:1 Medium parameters used: s = 0 mho/m, $e_r = 1$; density = 1000 kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: ER3DV6 SN2285; ConvF(1, 1, 1); Calibrated: 07/03/2008
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 05/03/2008
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - measurement distance from the probe sensor center to CD1880 Dipole = 10mm/Hearing Aid Compatibility Test

(5x19x1): Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 36.7 V/m; Power Drift = 0.040 dB

Maximum value of Total (measured) = 36.8 V/m

RTS RIM Testing Services		d Compatibility RF Emissio rry® Smartphone model R		Page 54(216)
Author Data	ates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW700	\mathbf{cw}

(41x181x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 37.4 V/m

Probe Modulation Factor = 1.00

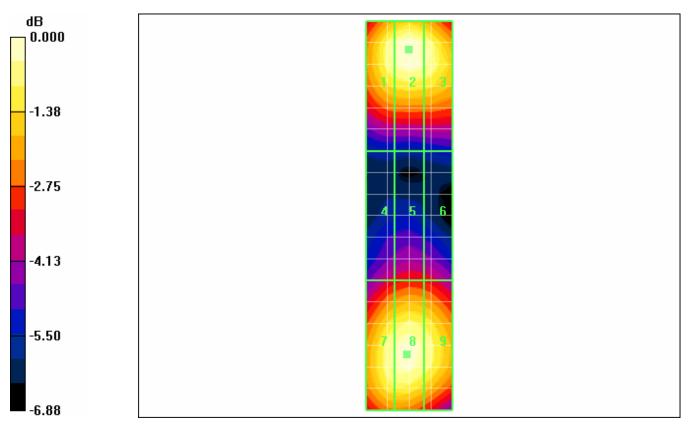
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 36.7 V/m; Power Drift = 0.040 dB

Peak E-field in V/m

Grid 1	Grid 2	Grid 3
36.3	37.4	36.3
M	M	M
4	4	4
Grid 4	Grid 5	Grid 6
25.3	26.2	25.8
\mathbf{M}	M	\mathbf{M}
4	4	4
Grid 7	Grid 8	Grid 9
36.0	36.5	35.3
M	M	M
4	4	4

RTS RIM Testing Services		I Compatibility RF Emissio rry® Smartphone model RI		Page 55(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	cw



0 dB = 37.4V/m

RTS RIM Testing Services		I Compatibility RF Emission rry® Smartphone model RI		Page 56(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	CW

Date/Time: 26/09/2008 1:07:53 PM

Test Laboratory: RTS

File Name: HAC_E_Dipole_AM_1880_PMF_CDMA.da4

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: Not Specified

Program Name: HAC RF E Dipole

Communication System: CW; Frequency: 1880 MHz; Duty Cycle: 1:1 Medium parameters used: s = 0 mho/m, $e_r = 1$; density = 1000 kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: ER3DV6 SN2285; ConvF(1, 1, 1); Calibrated: 07/03/2008
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 05/03/2008
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - measurement distance from the probe sensor center to CD1880 Dipole = 10mm/Hearing Aid Compatibility Test

(5x19x1): Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 23.5 V/m; Power Drift = -0.003 dB

Maximum value of Total (measured) = 23.6 V/m

RTS RIM Testing Services	_	d Compatibility RF Emissio rry® Smartphone model R		Page 57(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008 RTS-1191-0809-30 Rev 1 L6ARBW70C		cw	

(41x181x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 24.0 V/m

Probe Modulation Factor = 1.00

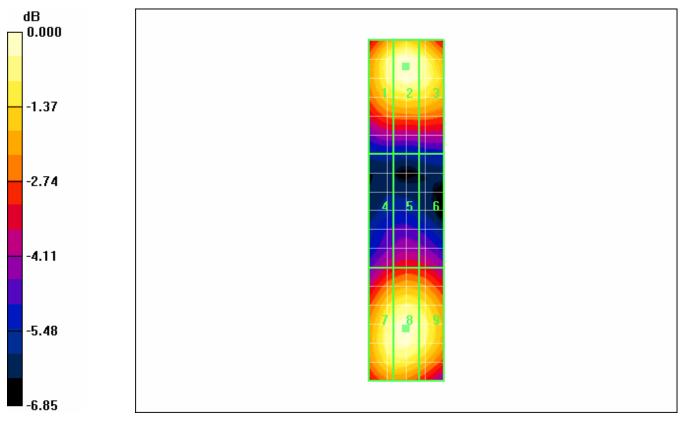
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 23.5 V/m; Power Drift = -0.003 dB

Peak E-field in V/m

Grid 1	Grid 2	Grid 3
23.2	24.0	23.3
M	M	\mathbf{M}
4	4	4
Grid 4	Grid 5	Grid 6
16.2	16.8	16.5
M	M	\mathbf{M}
4	4	4
Grid 7	Grid 8	Grid 9
23.1	23.5	22.8
M	M	\mathbf{M}
4	4	4

RTS RIM Testing Services		I Compatibility RF Emissio rry® Smartphone model RI		Page 58(216)
Author Data	Pates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	CW



 $0\ dB = 24.0V/m$

RTS RIM Testing Services		d Compatibility RF Emission rry® Smartphone model RI		Page 59(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW700	CW

Date/Time: 26/09/2008 1:56:46 PM

Test Laboratory: RTS

File Name: HAC_E_Dipole_CDMA1880.da4

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: Not Specified

Program Name: HAC RF E Dipole

Communication System: CDMA 1900; Frequency: 1880 MHz; Duty Cycle: 1:1

Medium parameters used: s = 0 mho/m, $e_r = 1$; density = 1000 kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: ER3DV6 SN2285; ConvF(1, 1, 1); Calibrated: 07/03/2008
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 05/03/2008
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - measurement distance from the probe sensor center to CD1880 Dipole = 10mm/Hearing Aid Compatibility Test

(5x19x1): Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 43.7 V/m; Power Drift = -0.133 dB

Maximum value of Total (measured) = 42.5 V/m

RTS	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RBW71CW			Page 60(216)
RIM Testing Services	00(210)			00(210)
Author Data	Dates of Test Report No FCC ID			-
Daoud Attayi	Aug 26, Sep 26-27, 2008 RTS-1191-0809-30 Rev 1 L6ARBW70C		$\mathbf{c}\mathbf{w}$	

(41x181x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 43.0 V/m

Probe Modulation Factor = 1.00

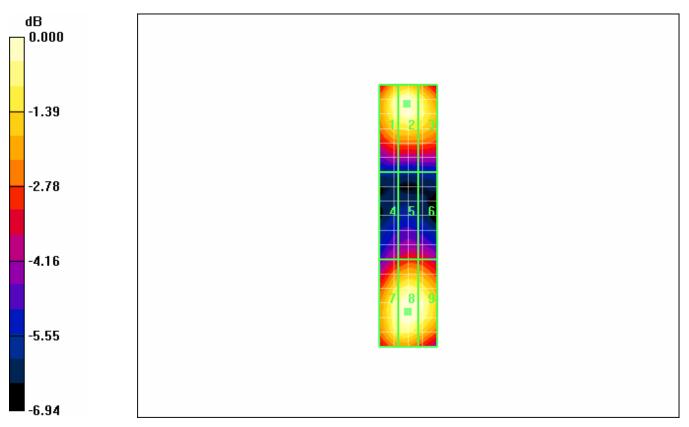
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 43.7 V/m; Power Drift = -0.133 dB

Peak E-field in V/m

Grid 1	Grid 2	Grid 3
41.9	43.0	40.8
M	M	M
4	4	4
Grid 4	Grid 5	Grid 6
28.8	30.3	29.9
M	${f M}$	${f M}$
4	4	4
Grid 7	Grid 8	Grid 9
41.6	42.8	42.0
M	M	M
4	4	4

RTS RIM Testing Services		l Compatibility RF Emission rry® Smartphone model RI		Page 61(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008 RTS-1191-0809-30 Rev 1 L6ARBW700			CW



0 dB = 43.0V/m

RTS RIM Testing Services		I Compatibility RF Emission rry® Smartphone model RI		Page 62(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	$\mathbf{c}\mathbf{w}$

Date/Time: 26/08/2008 10:46:01 AM

Test Laboratory: RTS

File Name: HAC_H_Dipole_CW835_20.00dBm.da4

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: Not Specified

Program Name: HAC RF H3DV6 Dipole

Communication System: CW; Frequency: 835 MHz; Duty Cycle: 1:1 Medium parameters used: s = 0 mho/m, $e_r = 1$; density = 1 kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: H3DV6 SN6105; ; Calibrated: 09/11/2007
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 05/03/2008
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x37x1):

Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.444 A/m: Power Drift = 0.063 dB

Maximum value of Total (measured) = 0.428 A/m

RTS RIM Testing Services		d Compatibility RF Emissio rry® Smartphone model R		Page 63(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW700	\mathbf{cw}

(41x361x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.428 A/m

Probe Modulation Factor = 1.00

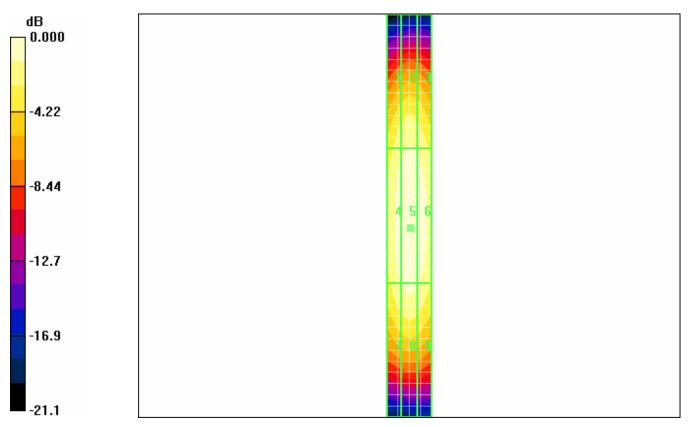
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.444 A/m; Power Drift = 0.063 dB

Peak H-field in A/m

Grid 1	Grid 2	Grid 3
0.352	0.372	0.360
M	M	\mathbf{M}
4	4	4
Grid 4	Grid 5	Grid 6
0.401	0.428	0.417
M	\mathbf{M}	\mathbf{M}
4	4	4
Grid 7	Grid 8	Grid 9
0.367	0.387	0.372
M	\mathbf{M}	M
4	4	4

RTS RIM Testing Services		d Compatibility RF Emission		Page 64(216)
Author Data	Dates of Test	tes of Test Report No FCC ID		
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	$\mathbf{c}\mathbf{w}$



0 dB = 0.428 A/m

RTS RIM Testing Services		d Compatibility RF Emission rry® Smartphone model RI		Page 65(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	CW

Date/Time: 26/09/2008 4:28:20 PM

Test Laboratory: RTS

File Name: HAC_H_Dipole_CW835_20dBm_09_26_08.da4

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: Not Specified

Program Name: HAC RF H3DV6 Dipole

Communication System: CW; Frequency: 835 MHz; Duty Cycle: 1:1 Medium parameters used: s = 0 mho/m, $e_r = 1$; density = 1 kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: H3DV6 SN6105; ; Calibrated: 09/11/2007
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 05/03/2008
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x37x1):

Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.446 A/m; Power Drift = 0.070 dB

Maximum value of Total (measured) = 0.425 A/m

RTS RIM Testing Services		l Compatibility RF Emissio rry® Smartphone model RI		Page 66(216)
Author Data	Oates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	CW

(41x361x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.427 A/m

Probe Modulation Factor = 1.00

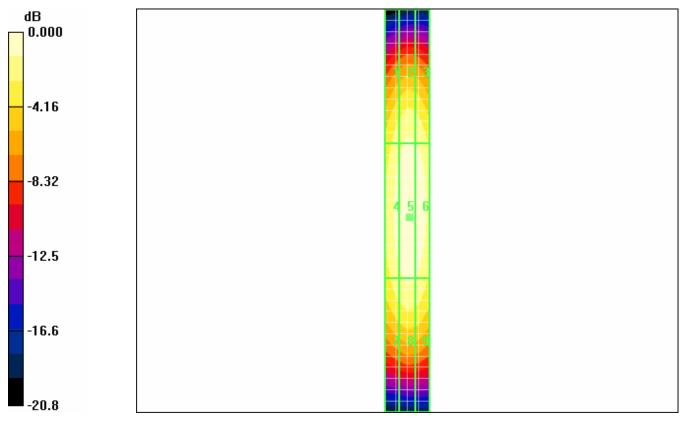
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.446 A/m; Power Drift = 0.070 dB

Peak H-field in A/m

Grid 1	Grid 2	Grid 3
0.351	0.376	0.369
M	M	M
4	4	4
Grid 4	Grid 5	Grid 6
0.393	0.427	0.418
M	M	\mathbf{M}
4	4	4
Grid 7	Grid 8	Grid 9
0.351	0.377	0.367
\mathbf{M}	\mathbf{M}	M
4	4	4

RTS RIM Testing Services		I Compatibility RF Emissio rry® Smartphone model RI		Page 67(216)
Author Data	Oates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	CW



0 dB = 0.427 A/m

RTS RIM Testing Services		I Compatibility RF Emission rry® Smartphone model RI		Page 68(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	CW

Date/Time: 26/09/2008 3:58:11 PM

Test Laboratory: RTS

File Name: HAC_H_Dipole_CW835_PMF_GSM.da4

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: Not Specified

Program Name: HAC RF H3DV6 Dipole

Communication System: CW; Frequency: 835 MHz; Duty Cycle: 1:1 Medium parameters used: s = 0 mho/m, $e_r = 1$; density = 1 kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 09/11/2007

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 05/03/2008
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x37x1):

Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.472 A/m; Power Drift = 0.082 dB

Maximum value of Total (measured) = 0.445 A/m

RTS RIM Testing Services	_	I Compatibility RF Emissio rry® Smartphone model R		Page 69(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW700	cw

(41x361x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.447 A/m

Probe Modulation Factor = 1.00

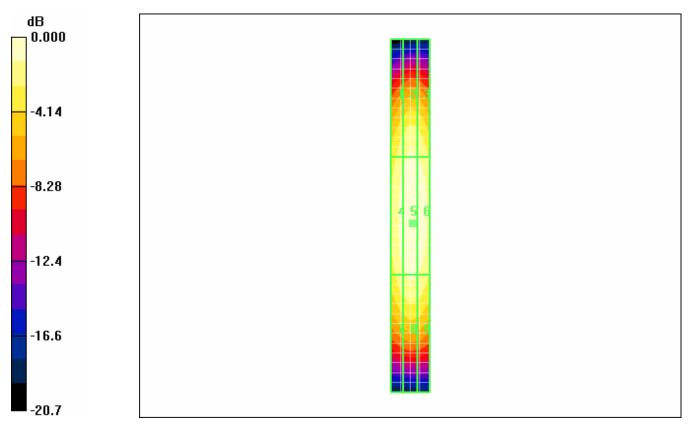
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.472 A/m; Power Drift = 0.082 dB

Peak H-field in A/m

Grid 1	Grid 2	Grid 3
0.370	0.396	0.386
M	M	M
4	4	4
Grid 4	Grid 5	Grid 6
0.413	0.447	0.438
\mathbf{M}	\mathbf{M}	\mathbf{M}
4	4	4
Grid 7	Grid 8	Grid 9
0.373	0.395	0.384
M	\mathbf{M}	M
4	4	4

RTS RIM Testing Services		d Compatibility RF Emission rry® Smartphone model RI		Page 70(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008 RTS-1191-0809-30 Rev 1 L6ARBW700			CW



0 dB = 0.447 A/m

RTS RIM Testing Services	_	I Compatibility RF Emissio rry® Smartphone model R		Page 71(216)
Author Data	Pates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	$\mathbf{c}\mathbf{w}$

Date/Time: 26/09/2008 4:06:30 PM

Test Laboratory: RTS

File Name: HAC_H_Dipole_AM835_PMF_GSM.da4

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: Not Specified

Program Name: HAC RF H3DV6 Dipole

Communication System: CW; Frequency: 835 MHz; Duty Cycle: 1:1 Medium parameters used: s = 0 mho/m, $e_r = 1$; density = 1 kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: H3DV6 SN6105; ; Calibrated: 09/11/2007
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 05/03/2008
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x37x1):

Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.299 A/m; Power Drift = -0.023 dB

Maximum value of Total (measured) = 0.282 A/m

RTS RIM Testing Services		l Compatibility RF Emissio rry® Smartphone model RI		Page 72(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	$\mathbf{c}\mathbf{w}$

(41x361x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.283 A/m

Probe Modulation Factor = 1.00

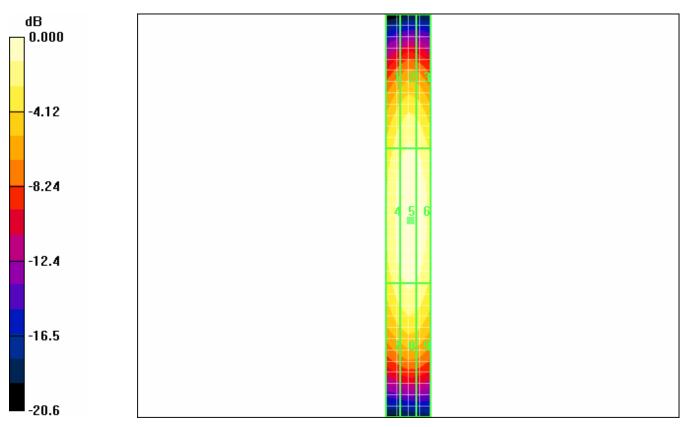
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.299 A/m; Power Drift = -0.023 dB

Peak H-field in A/m

Grid 1	Grid 2	Grid 3
0.232	0.249	0.243
M	M	M
4	4	4
Grid 4	Grid 5	Grid 6
0.259	0.283	0.277
M	M	M
4	4	4
Grid 7	Grid 8	Grid 9
0.234	0.250	0.242
M	M	M
4	4	4

RTS	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RBW71CW			Page 73(216)
RIM Testing Services	73(1			75(210)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	cw



0 dB = 0.283 A/m

RTS RIM Testing Services		I Compatibility RF Emission rry® Smartphone model RI		Page 74(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	CW

Date/Time: 26/09/2008 3:48:50 PM

Test Laboratory: RTS

File Name: HAC_H_Dipole_GSM835.da4

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: Not Specified

Program Name: HAC RF H3DV6 Dipole

Communication System: GSM 850; Frequency: 835 MHz; Duty Cycle: 1:8.3

Medium parameters used: s = 0 mho/m, $e_r = 1$; density = 1 kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 09/11/2007

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 05/03/2008

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8

Build 184

H Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x37x1):

Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.177 A/m; Power Drift = 0.084 dB

Maximum value of Total (measured) = 0.168 A/m

RTS RIM Testing Services	_	I Compatibility RF Emissio rry® Smartphone model R		Page 75(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	$\mathbf{c}\mathbf{w}$

(41x361x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.169 A/m

Probe Modulation Factor = 1.00

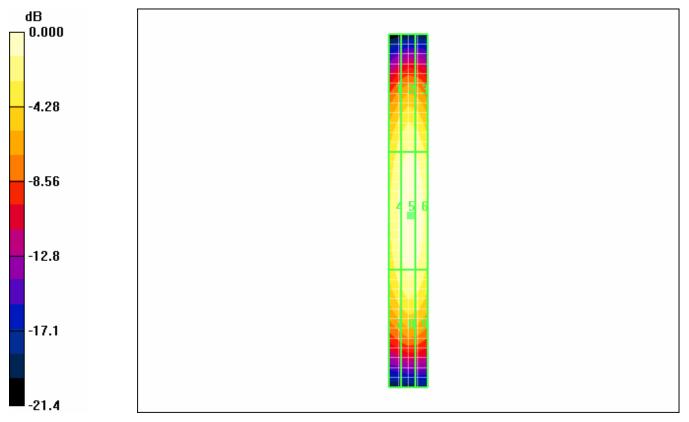
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.177 A/m; Power Drift = 0.084 dB

Peak H-field in A/m

Grid 1	Grid 2	Grid 3
0.135	0.147	0.142
\mathbf{M}	\mathbf{M}	M
4	4	4
Grid 4	Grid 5	Grid 6
0.153	0.169	0.165
\mathbf{M}	M	M
4	4	4
Grid 7	Grid 8	Grid 9
0.137	0.149	0.144
M	M	\mathbf{M}
4	4	4

RTS RIM Testing Services		d Compatibility RF Emission rry® Smartphone model RI		Page 76(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008 RTS-1191-0809-30 Rev 1 L6ARBW700			CW



0 dB = 0.169 A/m

RTS RIM Testing Services		d Compatibility RF Emission rry® Smartphone model RI		Page 77(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	CW

Date/Time: 26/09/2008 4:20:54 PM

Test Laboratory: RTS

File Name: HAC_H_Dipole_CW835_PMF_CDMA.da4

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: Not Specified

Program Name: HAC RF H3DV6 Dipole

Communication System: CW; Frequency: 835 MHz; Duty Cycle: 1:1 Medium parameters used: s = 0 mho/m, $e_r = 1$; density = 1 kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: H3DV6 SN6105; ; Calibrated: 09/11/2007
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 05/03/2008
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x37x1):

Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.156 A/m: Power Drift = -0.007 dB

Maximum value of Total (measured) = 0.147 A/m

RTS RIM Testing Services		d Compatibility RF Emissio rry® Smartphone model R		Page 78(216)
Author Data	ates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW700	$\mathbf{c}\mathbf{w}$

(41x361x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.148 A/m

Probe Modulation Factor = 1.00

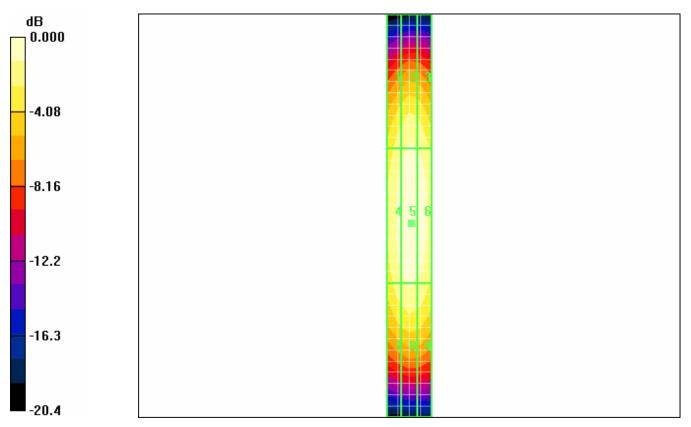
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.156 A/m; Power Drift = -0.007 dB

Peak H-field in A/m

Grid 1	Grid 2	Grid 3
0.122	0.130	0.127
\mathbf{M}	M	M
4	4	4
Grid 4	Grid 5	Grid 6
0.136	0.148	0.144
\mathbf{M}	\mathbf{M}	\mathbf{M}
4	4	4
Grid 7	Grid 8	Grid 9
0.122	0.130	0.126
M	\mathbf{M}	M
4	4	4

RTS RIM Testing Services		d Compatibility RF Emission rry® Smartphone model RI		Page 79(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008 RTS-1191-0809-30 Rev 1 L6ARBW70C		CW	



0 dB = 0.148 A/m

RTS RIM Testing Services		d Compatibility RF Emission rry® Smartphone model RI		Page 80(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	CW

Date/Time: 26/09/2008 4:13:23 PM

Test Laboratory: RTS

File Name: HAC_H_Dipole_AM835_PMF_CDMA.da4

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: Not Specified

Program Name: HAC RF H3DV6 Dipole

Communication System: CW; Frequency: 835 MHz; Duty Cycle: 1:1 Medium parameters used: s = 0 mho/m, $e_r = 1$; density = 1 kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: H3DV6 SN6105; ; Calibrated: 09/11/2007
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 05/03/2008
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x37x1):

Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.099 A/m: Power Drift = -0.045 dB

Maximum value of Total (measured) = 0.093 A/m

RTS RIM Testing Services	_	d Compatibility RF Emissio rry® Smartphone model R		Page 81(216)
Author Data	lates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW700	$\mathbf{c}\mathbf{w}$

(41x361x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.094 A/m

Probe Modulation Factor = 1.00

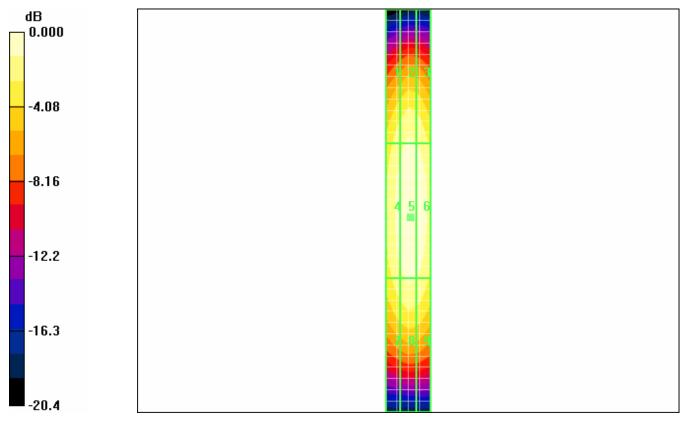
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.099 A/m; Power Drift = -0.045 dB

Peak H-field in A/m

Grid 1	Grid 2	Grid 3
0.078	0.083	0.081
M 4	0.083 M 4	0.081 M 4
Grid 4	Grid 5	Grid 6
0.086	0.094	0.092
M	M	M
4	4	4
Grid 7	Grid 8	Grid 9
0.078	0.083	0.081
M	M	M
4	4	4

RTS RIM Testing Services		d Compatibility RF Emission rry® Smartphone model RI		Page 82(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008 RTS-1191-0809-30 Rev 1 L6ARBW70CW			CW



0 dB = 0.094 A/m

RTS RIM Testing Services		I Compatibility RF Emission rry® Smartphone model RI		Page 83(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	CW

Date/Time: 26/09/2008 3:36:36 PM

Test Laboratory: RTS

File Name: HAC_H_Dipole_CDMA835.da4

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: Not Specified

Program Name: HAC RF H3DV6 Dipole

Communication System: CDMA 800; Frequency: 835 MHz; Duty Cycle: 1:1

Medium parameters used: s = 0 mho/m, $e_r = 1$; density = 1 kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 09/11/2007

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 05/03/2008

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8

Build 184

H Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x37x1):

Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.158 A/m; Power Drift = 0.081 dB

Maximum value of Total (measured) = 0.152 A/m

RTS RIM Testing Services		d Compatibility RF Emissio rry® Smartphone model R		Page 84(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW700	$\mathbf{c}\mathbf{w}$

(41x361x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.153 A/m

Probe Modulation Factor = 1.00

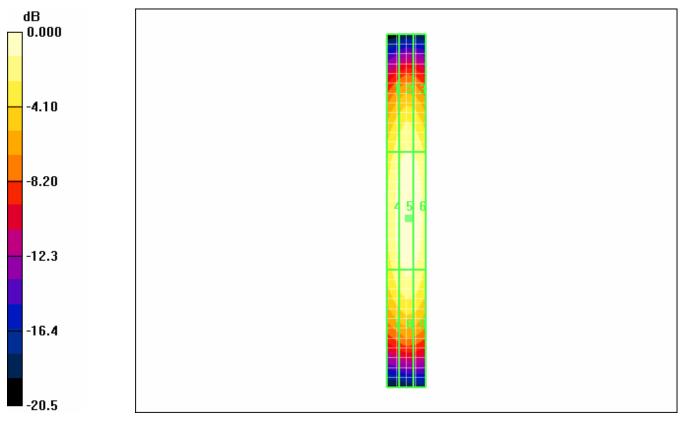
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.158 A/m; Power Drift = 0.081 dB

Peak H-field in A/m

Grid 1	Grid 2	Grid 3
0.124	0.134	0.130
\mathbf{M}	\mathbf{M}	M
4	4	4
Grid 4	Grid 5	Grid 6
0.140	0.153	0.150
\mathbf{M}	\mathbf{M}	\mathbf{M}
4	4	4
Grid 7	Grid 8	Grid 9
0.127	0.136	0.132
M	\mathbf{M}	M
4	4	4

RTS RIM Testing Services		I Compatibility RF Emission rry® Smartphone model RI		Page 85(216)
Author Data	ates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	CW



0 dB = 0.153 A/m

RTS RIM Testing Services		d Compatibility RF Emission rry® Smartphone model RI		Page 86(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	CW

Date/Time: 26/08/2008 11:00:12 AM

Test Laboratory: RTS

File Name: HAC_H_Dipole_CW1880_20.00dBm.da4

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: Not Specified

Program Name: HAC RF H3DV6 Dipole

Communication System: CW; Frequency: 1880 MHz; Duty Cycle: 1:1 Medium parameters used: s = 0 mho/m, $e_r = 1$; density = 1 kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: H3DV6 SN6105; ; Calibrated: 09/11/2007
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 05/03/2008
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - measurement distance from the probe sensor center to CD1880 Dipole = 10mm/Hearing Aid Compatibility Test

(5x19x1): Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.447 A/m; Power Drift = -0.012 dB

Maximum value of Total (measured) = 0.423 A/m

RTS RIM Testing Services		d Compatibility RF Emissio rry® Smartphone model R		Page 87(216)
Author Data	ates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW700	\mathbf{cw}

(41x181x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.424 A/m

Probe Modulation Factor = 1.00

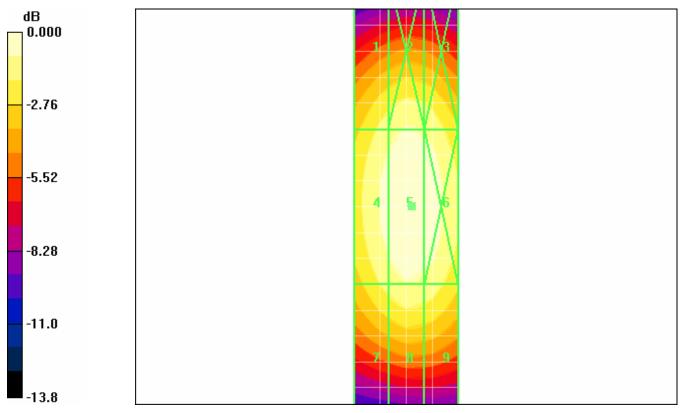
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.447 A/m; Power Drift = -0.012 dB

Peak H-field in A/m

Grid 1 0.365	Grid 2 0.386	Grid 3 0.378
\mathbf{M}	\mathbf{M}	M
Grid 4	2 Grid 5	2 Grid 6
0.399	0.424	0.415
M	\mathbf{M}	M
2	2	2
Grid 7	Grid 8	Grid 9
0.358	0.379	0.371
M	\mathbf{M}	\mathbf{M}
2	2	2

RTS RIM Testing Services		d Compatibility RF Emission rry® Smartphone model RI		Page 88(216)
Author Data	Pates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	$\mathbf{c}\mathbf{w}$



0 dB = 0.424 A/m

RTS RIM Testing Services	_	d Compatibility RF Emission rry® Smartphone model RI		Page 89(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	CW

Date/Time: 26/09/2008 5:27:46 PM

Test Laboratory: RTS

File Name: HAC_H_Dipole_CW1880_20dBm_09_26_08.da4

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: Not Specified

Program Name: HAC RF H3DV6 Dipole

Communication System: CW; Frequency: 1880 MHz; Duty Cycle: 1:1 Medium parameters used: s = 0 mho/m, $e_r = 1$; density = 1 kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: H3DV6 SN6105; ; Calibrated: 09/11/2007
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 05/03/2008
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - measurement distance from the probe sensor center to CD1880 Dipole = 10mm/Hearing Aid Compatibility Test

(5x19x1): Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.463 A/m; Power Drift = 0.004 dB

Maximum value of Total (measured) = 0.439 A/m

RTS RIM Testing Services	_	d Compatibility RF Emissio rry® Smartphone model R		Page 90(216)
Author Data	ates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	cw

(41x181x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.442 A/m

Probe Modulation Factor = 1.00

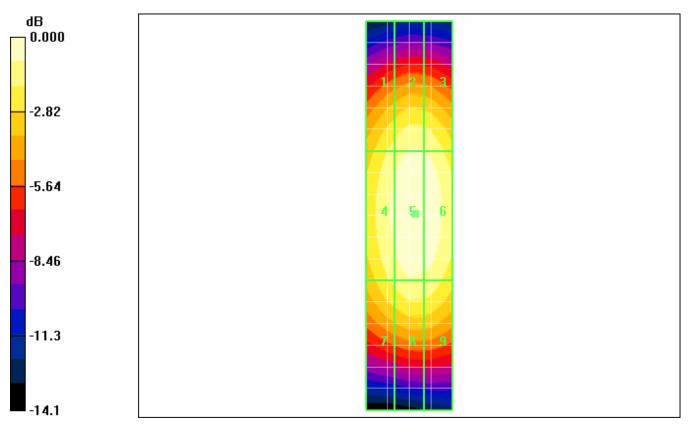
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.463 A/m; Power Drift = 0.004 dB

Peak H-field in A/m

Grid 1 0.373	Grid 2 0.404	Grid 3 0.399
M 2	M 2	M 2
Grid 4 0.408	Grid 5 0.442	Grid 6 0.436
M 2	M 2	M 2
Grid 7	Grid 8	Grid 9
0.367	0.394	0.388
M	\mathbf{M}	M
2	2	2

RTS RIM Testing Services		d Compatibility RF Emission rry® Smartphone model RI		Page 91(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	CW



0 dB = 0.442 A/m

RTS RIM Testing Services		d Compatibility RF Emission rry® Smartphone model RI		Page 92(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	CW

Date/Time: 26/09/2008 5:05:10 PM

Test Laboratory: RTS

File Name: HAC_H_Dipole_CW1880_PMF_GSM.da4

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: Not Specified

Program Name: HAC RF H3DV6 Dipole

Communication System: CW; Frequency: 1880 MHz; Duty Cycle: 1:1 Medium parameters used: s = 0 mho/m, $e_r = 1$; density = 1 kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: H3DV6 SN6105; ; Calibrated: 09/11/2007
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 05/03/2008
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - measurement distance from the probe sensor center to CD1880 Dipole = 10mm/Hearing Aid Compatibility Test

(5x19x1): Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.336 A/m; Power Drift = -0.004 dB

Maximum value of Total (measured) = 0.319 A/m

RTS RIM Testing Services		d Compatibility RF Emissio rry® Smartphone model R		Page 93(216)
Author Data	Pates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW700	\mathbf{cw}

(41x181x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.321 A/m

Probe Modulation Factor = 1.00

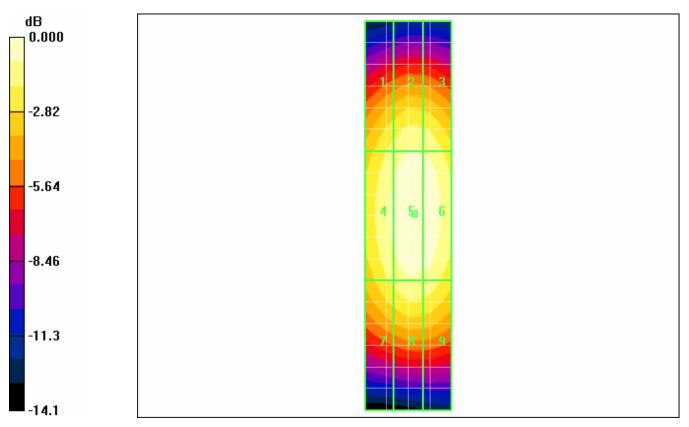
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.336 A/m; Power Drift = -0.004 dB

Peak H-field in A/m

Grid 1	Grid 2	Grid 3
0.270	0.292	0.289
M	M	\mathbf{M}
3	3	3
Grid 4	Grid 5	Grid 6
0.296	0.321	0.316
\mathbf{M}	\mathbf{M}	\mathbf{M}
3	3	3
Grid 7	Grid 8	Grid 9
0.266	0.286	0.282
M	\mathbf{M}	M
3	3	3

RTS RIM Testing Services		d Compatibility RF Emission rry® Smartphone model RI		Page 94(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	CW



0 dB = 0.321 A/m

RTS RIM Testing Services		d Compatibility RF Emission rry® Smartphone model RI		Page 95(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW700	cw

Date/Time: 26/09/2008 5:09:43 PM

Test Laboratory: RTS

File Name: HAC_H_Dipole_AM1880_PMF_GSM.da4

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: Not Specified

Program Name: HAC RF H3DV6 Dipole

Communication System: CW; Frequency: 1880 MHz; Duty Cycle: 1:1 Medium parameters used: s = 0 mho/m, $e_r = 1$; density = 1 kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: H3DV6 SN6105; ; Calibrated: 09/11/2007
- Sensor-Surface: 0mm (Fix Surface) Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 05/03/2008
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - measurement distance from the probe sensor center to CD1880 Dipole = 10mm/Hearing Aid Compatibility Test

(5x19x1): Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.216 A/m; Power Drift = 0.018 dB

Maximum value of Total (measured) = 0.204 A/m

RTS RIM Testing Services		d Compatibility RF Emissio rry® Smartphone model R		Page 96(216)
Author Data	Pates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW700	$\mathbf{C}\mathbf{W}$

(41x181x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.205 A/m

Probe Modulation Factor = 1.00

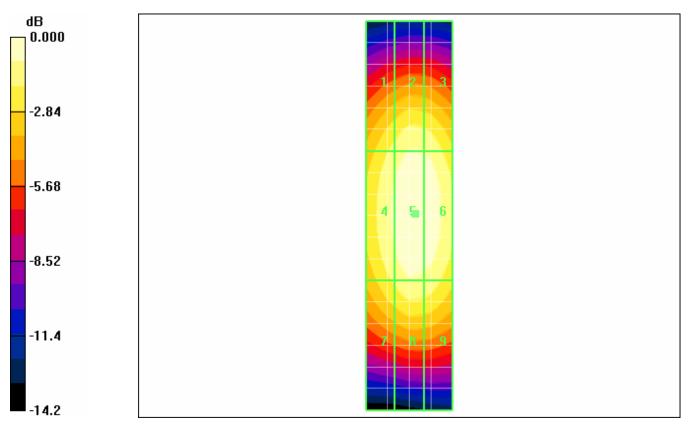
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.216 A/m; Power Drift = 0.018 dB

Peak H-field in A/m

Grid 1	Grid 2	Grid 3
0.172	0.186	0.184
M	M	M
4	4	4
Grid 4	Grid 5	Grid 6
0.188	0.205	0.202
\mathbf{M}	\mathbf{M}	\mathbf{M}
4	3	3
Grid 7	Grid 8	Grid 9
0.169	0.183	0.180
M	\mathbf{M}	M
4	4	4

RTS RIM Testing Services		I Compatibility RF Emissio rry® Smartphone model RI		Page 97(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	CW



0 dB = 0.205 A/m

RTS RIM Testing Services		I Compatibility RF Emission rry® Smartphone model RI		Page 98(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	cw

Date/Time: 26/09/2008 4:39:54 PM

Test Laboratory: RTS

File Name: HAC_H_Dipole_GSM1880.da4

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: Not Specified

Program Name: HAC RF H3DV6 Dipole

Communication System: GSM 1900; Frequency: 1880 MHz; Duty Cycle: 1:8.3

Medium parameters used: s = 0 mho/m, $e_r = 1$; density = 1 kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 09/11/2007

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 05/03/2008

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8

Build 184

H Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x37x1):

Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.135 A/m; Power Drift = -0.063 dB

Maximum value of Total (measured) = 0.127 A/m

RTS RIM Testing Services		d Compatibility RF Emissio rry® Smartphone model R		Page 99(216)
Author Data	ates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW700	\mathbf{cw}

(41x361x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.127 A/m

Probe Modulation Factor = 1.00

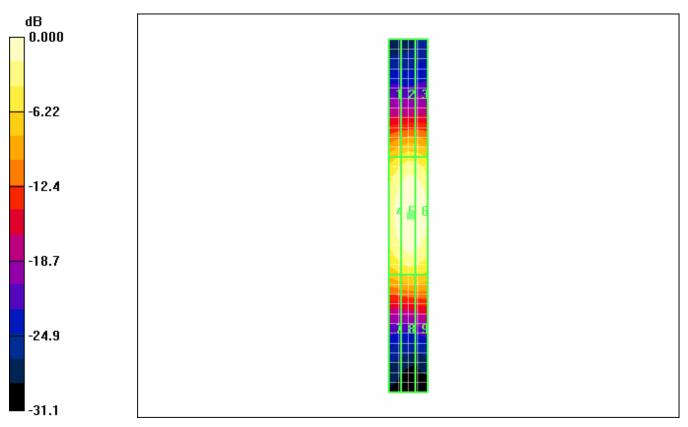
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.135 A/m; Power Drift = -0.063 dB

Peak H-field in A/m

Grid 1 0.067	Grid 2 0.073	Grid 3 0.071
M 4	M 4	M 4
Grid 4 0.115	Grid 5 0.127	Grid 6 0.124
M 4	M 4	M 4
Grid 7	Grid 8	Grid 9
0.061	0.066	0.065
M	\mathbf{M}	M
4	4	4

RTS RIM Testing Services		I Compatibility RF Emissio rry® Smartphone model RI		Page 100(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	$\mathbf{c}\mathbf{w}$



0 dB = 0.127 A/m

RTS RIM Testing Services	_	I Compatibility RF Emissio		Page 101(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	$\mathbf{c}\mathbf{w}$

Date/Time: 26/09/2008 5:18:21 PM

Test Laboratory: RTS

File Name: HAC_H_Dipole_CW1880_PMF_CDMA.da4

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: Not Specified

Program Name: HAC RF H3DV6 Dipole

Communication System: CW; Frequency: 1880 MHz; Duty Cycle: 1:1 Medium parameters used: s = 0 mho/m, $e_r = 1$; density = 1 kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: H3DV6 SN6105; ; Calibrated: 09/11/2007
- Sensor-Surface: 0mm (Fix Surface) Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 05/03/2008
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - measurement distance from the probe sensor center to CD1880 Dipole = 10mm/Hearing Aid Compatibility Test

(5x19x1): Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.160 A/m; Power Drift = -0.001 dB

Maximum value of Total (measured) = 0.151 A/m

RTS RIM Testing Services		I Compatibility RF Emissio rry® Smartphone model RI		Page 102(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	$\mathbf{c}\mathbf{w}$

(41x181x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.152 A/m

Probe Modulation Factor = 1.00

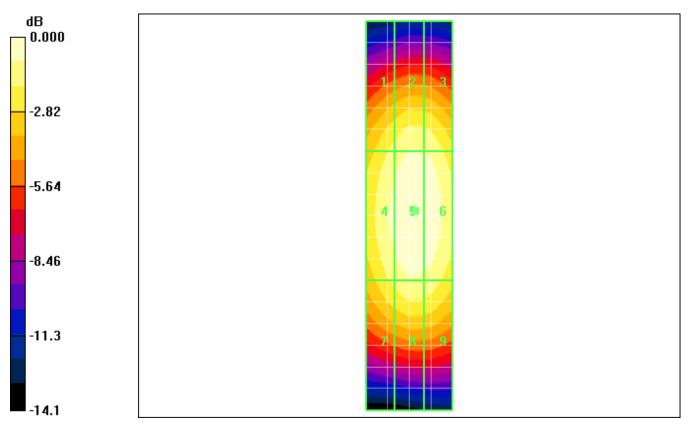
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.160 A/m; Power Drift = -0.001 dB

Peak H-field in A/m

Grid 1	Grid 2	Grid 3
0.128 M	0.138 M	0.137 M
4	4	4
Grid 4	Grid 5	Grid 6
0.141	0.152	0.150
\mathbf{M}	\mathbf{M}	\mathbf{M}
4	4	4
Grid 7	Grid 8	Grid 9
0.126	0.136	0.133
M	\mathbf{M}	\mathbf{M}
4	4	4

RTS RIM Testing Services		d Compatibility RF Emission rry® Smartphone model RI		Page 103(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	CW



0 dB = 0.152 A/m

RTS RIM Testing Services	_	d Compatibility RF Emission rry® Smartphone model RI		Page 104(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008 RTS-1191-0809-30 Rev 1 L6ARBW70C			CW

Date/Time: 26/09/2008 5:13:58 PM

Test Laboratory: RTS

File Name: HAC_H_Dipole_AM1880_PMF_CDMA.da4

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: Not Specified

Program Name: HAC RF H3DV6 Dipole

Communication System: CW; Frequency: 1880 MHz; Duty Cycle: 1:1 Medium parameters used: s = 0 mho/m, $e_r = 1$; density = 1 kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: H3DV6 SN6105; ; Calibrated: 09/11/2007
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 05/03/2008
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - measurement distance from the probe sensor center to CD1880 Dipole = 10mm/Hearing Aid Compatibility Test

(5x19x1): Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.088 A/m; Power Drift = 0.056 dB

Maximum value of Total (measured) = 0.084 A/m

RTS RIM Testing Services		d Compatibility RF Emissio rry® Smartphone model R		Page 105(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008 RTS-1191-0809-30 Rev 1 L6ARBW70C		$\mathbf{c}\mathbf{w}$	

(41x181x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.085 A/m

Probe Modulation Factor = 1.00

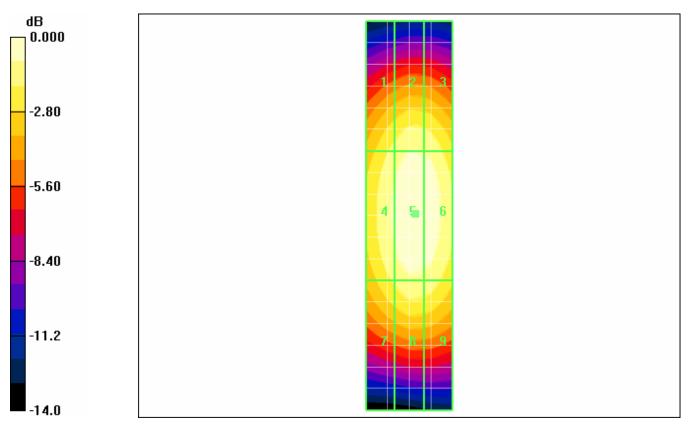
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.088 A/m; Power Drift = 0.056 dB

Peak H-field in A/m

Grid 1 0.071	Grid 2 0.077	Grid 3 0.076
M 4	M 4	M 4
Grid 4 0.078	Grid 5 0.085	Grid 6 0.083
M 4	M 4	M 4
Grid 7	Grid 8	Grid 9
0.070	0.075	0.074
M	\mathbf{M}	\mathbf{M}
4	4	4

RTS RIM Testing Services		d Compatibility RF Emission rry® Smartphone model RI		Page 106(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	CW



0 dB = 0.085 A/m

RTS RIM Testing Services		d Compatibility RF Emission rry® Smartphone model RI		Page 107(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008 RTS-1191-0809-30 Rev 1 L6ARBW70C			CW

Date/Time: 26/09/2008 4:49:44 PM

Test Laboratory: RTS

File Name: HAC_H_Dipole_CDMA1880.da4

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: Not Specified

Program Name: HAC RF H3DV6 Dipole

Communication System: CDMA 1900; Frequency: 1880 MHz; Duty Cycle: 1:1

Medium parameters used: s = 0 mho/m, $e_r = 1$; density = 1 kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: H3DV6 SN6105; ; Calibrated: 09/11/2007
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 05/03/2008
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x37x1):

Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.161 A/m; Power Drift = -0.141 dB

Maximum value of Total (measured) = 0.151 A/m

RTS RIM Testing Services	_	d Compatibility RF Emissio rry® Smartphone model R		Page 108(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	CW

(41x361x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.152 A/m

Probe Modulation Factor = 1.00

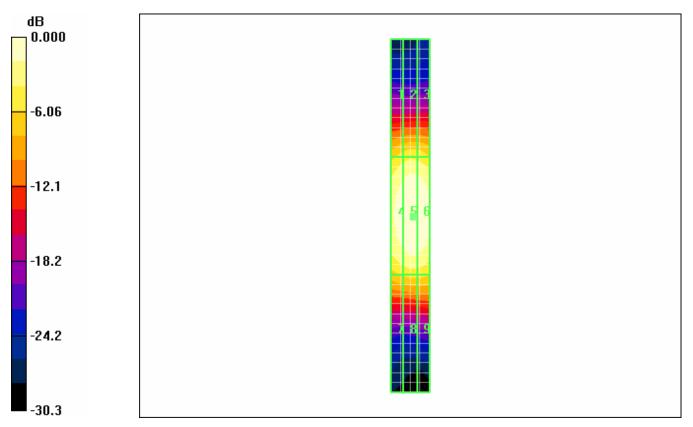
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.161 A/m; Power Drift = -0.141 dB

Peak H-field in A/m

Grid 1	Grid 2	Grid 3
0.087	0.092	0.090
M	M	M
4	4	4
Grid 4 0.140 M	Grid 5 0.152 M	Grid 6 0.150 M
Grid 7 0.079 M 4	Grid 8 0.084 M 4	Grid 9 0.084 M 4

RTS RIM Testing Services		d Compatibility RF Emission rry® Smartphone model RI		Page 109(216)
Author Data	Dates of Test			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	CW

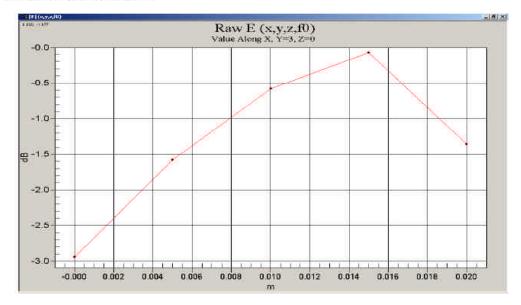


0 dB = 0.152 A/m

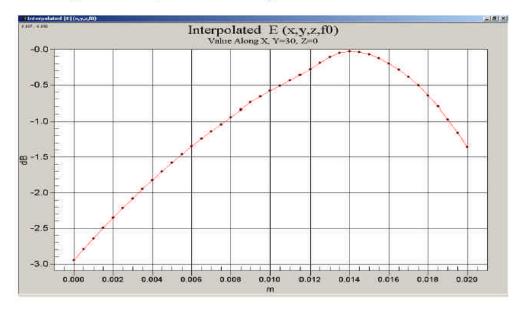
RTS RIM Testing Services	_	I Compatibility RF Emissio rry® Smartphone model RI		Page 110(216)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70CW	

Justification of Step Size and Interpolation

This section demonstrates that a 5mm step size with interpolation provides sufficient resolution for RF emissions measurements. The DASY 4 uses interpolation algorithms to derive 9 interpolated points between every measured point.

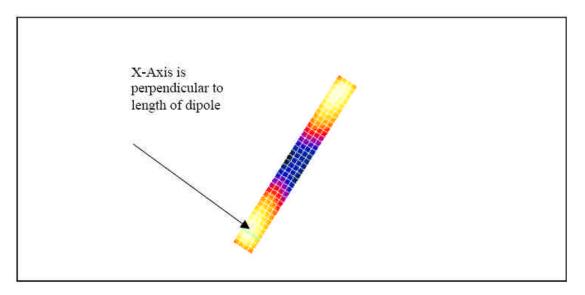


The figure above shows the raw measured field strength perpendicular to the length of the validation dipole. The TCB guidance slides require the 3dB width to be much larger than the step size. The width between -3dB points is ≥ 21 mm, at least 4 times the step size.



This figure shows the interpolated field strength perpendicular to the dipole. The interpolated points follow the raw points with no inconsistencies.

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The green line in this figure shows the axis along which the points lie.

Comparison of 5mm and 2mm step sizes

An additional set of measurements was taken: dipole validations were performed using 5mm and 2mm step sizes. The delta between the two readings is insignificant for both field types (< 0.4% for E and 0% for H), demonstrating that 5mm is sufficient. The plots follow.

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Date/Time: 14/07/2005 11:35:24 AM

Lab: RIM Testing Services (RTS)

Dipole Validation 1880 MHz_E-Field 07_14_05

DUT: HAC Dipole 1880 MHz; Type: CD1880V3

Communication System: CW; Frequency: 1880 MHz; Duty Cycle: 1:1 Medium: Air Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 1000$ kg/m³

Phantom section: H Device Section

DASY4 Configuration:

- Probe: ER3DV6 SN2285; ConvF(1, 1, 1); Calibrated: 10/12/2004
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 03/01/2005
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
 Measurement SW: DASY4, V4.5 Build 19; Postprocessing SW: SEMCAD, V1.8 Build 146

E Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (5x19x1):

Measurement grid: dx=5mm, dy=5mm

Maximum value of Total (measured) = 134.8 V/m

E Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (41x181x1):

Measurement grid: dx=5mm, dy=5mm Maximum value of Total field (slot averaged) = 131.0 V/m

Hearing Aid Near-Field Category: M2 (AWF 0 dB)

E in V/m (Time averaged) E in V/m (Slot averaged)

_	1111 17	(1	e a reraj	5000)	D III TO	iii (Diot	areius
			Grid 3		Grid 1	Grid 2	Grid 3
1	123.2	138.1	138.4		123.2	138.1	138.4
(Grid 4	Grid 5	Grid 6		Grid 4	Grid 5	Grid 6
8	80.9	92.3	92.2		80.9	92.3	92.2
			Grid 9		Grid 7		
1	119.8	131.0	130.7		119.8	131.0	130.7

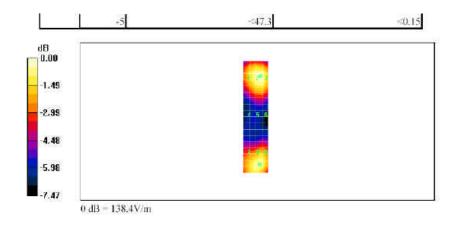
AWF (dB)	Limits for E-Field Emissions (V/m)	Limits for H-Field Emissions (A/m)
0	199.5 - 354.8	0.6 - 1.07
-5	149.6 - 266.1	0.45 - 0.8
0	112.2 - 199.5	0.34 - 0.6
-5	84.1 - 149.6	0.25 - 0.45
0	63.1 - 112.2	0.19 - 0.34
-5	47.3 - 84.1	0.15 - 0.25
0	<63.1	<0.19
	0	0 112.2 - 199.5 -5 84.1 - 149.6 0 63.1 - 112.2 -5 47.3 - 84.1

file://C:\Program%20Files\DASY4\Print Templates\Dipole%20Validation%201880%20... 14/07/2005

RTS RIM Testing Services		I Compatibility RF Emissio rry® Smartphone model RI		Page 113(216)	
Author Data	ates of Test Report No FCC ID				
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70CW		

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Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70CW	

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Date/Time: 14/07/2005 11:44:51 AM

Lab: RIM Testing Services (RTS)

Dipole Validation 1880 MHz_2mm step_E-Field 07_14_05

DUT: HAC Dipole 1880 MHz; Type: CD1880V3

Communication System: CW; Frequency: 1880 MHz; Duty Cycle: 1:1 Medium: Air Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 1000$ kg/m³

Phantom section: H Device Section

DASY4 Configuration:

- Probe: ER3DV6 SN2285; ConvF(1, 1, 1); Calibrated: 10/12/2004
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 03/01/2005
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
 Measurement SW: DASY4, V4.5 Build 19; Postprocessing SW: SEMCAD, V1.8 Build 146

E Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (11x46x1):

Measurement grid: dx=2mm, dy=2mm

Maximum value of Total (measured) = 138.0 V/m

E Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (101x451x1):

Measurement grid: dx=2mm, dy=2mm

Maximum value of Total field (slot averaged) = 131.2 V/m

Hearing Aid Near-Field Category: M2 (AWF 0 dB)

E in V/m (Time averaged) E in V/m (Slot averaged)

Bill Will (Time a enaged) Bill Will (Biet a enage						
Grid 1	Grid 2	Grid 3		Grid 1	Grid 2	Grid 3
123.1	138.6	138.6		123.1	138.6	138.6
Grid 4	Grid 5	Grid 6		Grid 4	Grid 5	Grid 6
81.4	92.1	91.6		81.4	92.1	91.6
Grid 7				Grid 7		
121.3	131.2	131.0		121.3	131.2	131.0

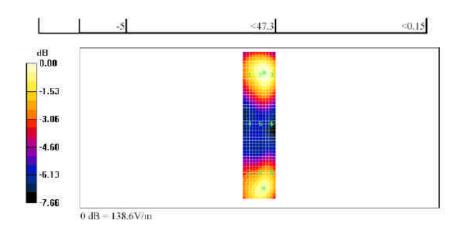
Category	AWF (dB)	Limits for E-Field Emissions (V/m)	Limits for H-Field Emissions (A/m)
M1	0	199.5 - 354.8	0.6 - 1.07
	-5	149.6 - 266.1	0.45 - 0.8
M2	0	112.2 - 199.5	0.34 - 0.6
	-5	84.1 - 149.6	0.25 - 0.45
М3	0	63.1 - 112.2	0.19 - 0.34
	-5	47.3 - 84.1	0.15 - 0.25
M4	0	<63.1	<0.19

file://C:\Program%20Files\DASY4\Print Templates\Dipole%20Validation%201880%20... 14/07/2005

RTS RIM Testing Services		l Compatibility RF Emissio rry® Smartphone model RI		Page 115(216)	
Author Data	ates of Test Report No FCC ID				
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70CW		

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file://C:\Program%20Files\DASY4\Print_Templates\Dipole%20Validation%201880%20... 14/07/2005

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Date/Time: 14/07/2005 12:43:02 PM

Lab: RIM Testing Services (RTS)

HAC_H_Dipole_CW 1880_5 mm step_07_14_05

DUT: HAC Dipole 1880 MHz; Type: CD1880V3

Communication System: CW; Frequency: 1880 MHz; Duty Cycle: 1:1 Medium: Air Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 1$ kg/m³

Phantom section: H Dipole Section

DASY4 Configuration:

- Probe: H3DV6 SN6105; ; Calibrated: 10/12/2004
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
 Electronics: DAE3 Sn472; Calibrated: 03/01/2005

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
 Measurement SW: DASY4, V4.5 Build 19; Postprocessing SW: SEMCAD, V1.8 Build 146

H Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (5x19x1):

Measurement grid: dx=5mm, dy=5mm Maximum value of Total (measured) = 0.406 A/m

H Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (41x181x1):

Measurement grid: dx=5mm, dy=5mm

Maximum value of Total field (slot averaged) = 0.406 A/m

Hearing Aid Near-Field Category: M2 (AWF 0 dB)

H in A/m (Time averaged) H in A/m (Slot averaged)

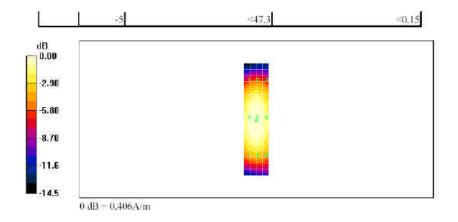
Grid 1	Grid 2	Grid 3	ĪΊ	Grid 1	Grid 2	Grid 3
0.342				0.342		
Grid 4	Grid 5	Grid 6	1	Grid 4	Grid 5	Grid 6
0.389	0.406	0.389		0.389	0.406	0.389
Grid 7	Grid 8	Grid 9	1	Grid 7	Grid 8	Grid 9
0.363	0.378	0.363		0.363	0.378	0.363

Category	AWF (dB)	Limits for E-Field Emissions (V/m)	Limits for H-Field Emissions (A/m)
M1	0	199.5 - 354.8	0.6 - 1.07
	-5	149.6 - 266.1	0.45 - 0.8
M2	0	112.2 - 199.5	0.34 - 0.6
	-5	84.1 - 149.6	0.25 - 0.45
М3	0	63.1 - 112.2	0.19 - 0.34
	-5	47.3 - 84.1	0.15 - 0.25
M4	0	<63.1	<0.19

file://C:\Program%20Files\DASY4\Print_Templates\HAC_H_Dipole_CW%201880_5%... 14/07/2005

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Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	\mathbf{cw}

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Date/Time: 14/07/2005 12:53:40 PM

Lab: RIM Testing Services (RTS)

HAC_H_Dipole_CW 1880_2 mm step_07_14_05

DUT: HAC Dipole 1880 MHz; Type: CD1880V3

Communication System: CW; Frequency: 1880 MHz; Duty Cycle: 1:1 Medium: Air Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 1$ kg/m³

Phantom section: H Dipole Section

DASY4 Configuration:

- Probe: H3DV6 SN6105; ; Calibrated: 10/12/2004
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 03/01/2005
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
 Measurement SW: DASY4, V4.5 Build 19; Postprocessing SW: SEMCAD, V1.8 Build 146

H Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (11x46x1):

Measurement grid: dx=2mm, dy=2mm

Maximum value of Total (measured) = 0.406 A/m

H Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (101x451x1):

Measurement grid: dx=2mm, dy=2mm

Maximum value of Total field (slot averaged) = 0.406 A/m

Hearing Aid Near-Field Category: M2 (AWF 0 dB)

H in A/m (Time averaged) H in A/m (Slot averaged)

Grid 1	Grid 2	Grid 3	Grid 1	Grid 2	Grid 3
0.347	0.361	0.348	0.347	0.361	0.348
Grid 4	Grid 5	Grid 6	Grid 4	Grid 5	Grid 6
0.394	0.406	0.391	0.394	0.406	0.391
Grid 7	Grid 8	Grid 9	Grid 7	Grid 8	Grid 9
0.367	0.380	0.365	0.367	0.380	0.365

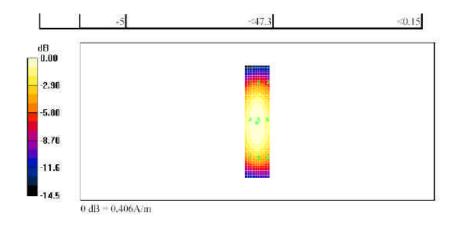
Category	AWF (dB)	Limits for E-Field Emissions (V/m)	Limits for H-Field Emissions (A/m)
M1	0	199.5 - 354.8	0.6 - 1.07
	-5	149.6 - 266.1	0.45 - 0.8
M2	0	112.2 - 199.5	0.34 - 0.6
	-5	84.1 - 149.6	0.25 - 0.45
М3	0	63.1 - 112.2	0.19 - 0.34
	-5	47.3 - 84.1	0.15 - 0.25
M4	0	<63.1	<0.19

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Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	CW

Date/Time: 14/07/2005 12:53:40 PM

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file://C:\Program%20Files\DASY4\Print_Templates\HAC_H_Dipole_CW%201880_2%... 14/07/2005

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Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	CW

A.3 RF emissions and ambient noise plots

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Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	$\mathbf{c}\mathbf{w}$

Date/Time: 26/08/2008 11:15:42 AM

Test Laboratory: RTS

File Name: HAC_E_GSM850_Low_Chan.da4

DUT: BlackBerry Smartphone; Type: Sample; Serial: Not Specified

Program Name: HAC RF ER3D Device

Communication System: GSM 850; Frequency: 824.2 MHz; Duty Cycle: 1:8.3

Medium parameters used: s = 0 mho/m, $e_r = 1$; density = 1000 kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: ER3DV6 SN2285; ConvF(1, 1, 1); Calibrated: 07/03/2008
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472: Calibrated: 05/03/2008
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8

Build 184

E Scan - ER3D - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 73.2 V/m; Power Drift = -0.114 dB

Maximum value of Total (measured) = 60.0 V/m

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Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	CW

E Scan - ER3D - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Measurement

grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 184.9 V/m

Probe Modulation Factor = 3.07

Device Reference Point: 0.000, 0.000, 353.7 mm

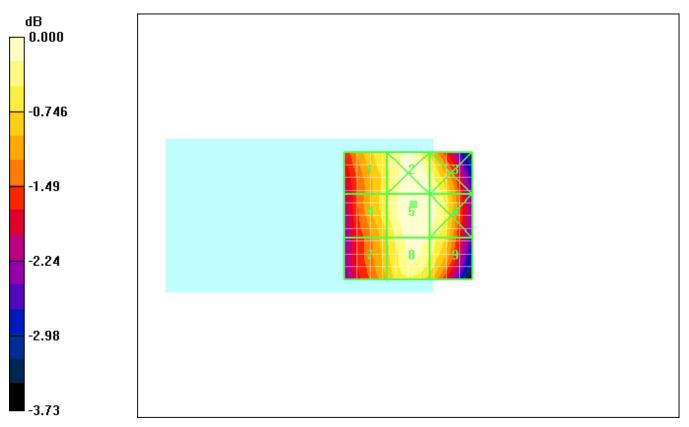
Reference Value = 73.2 V/m; Power Drift = -0.114 dB

Hearing Aid Near-Field Category: M3 (AWF -5 dB)

Peak E-field in V/m

Grid 1	Grid 2	Grid 3
174.7	184.3	181.7
M	\mathbf{M}	M
3	3	3
Grid 4	Grid 5	Grid 6
174.0	184.9	182.9
M	M	M
3	3	3
Grid 7	Grid 8	Grid 9
169.4	182.0	178.6
M	\mathbf{M}	\mathbf{M}
3	3	3

RTS RIM Testing Services		l Compatibility RF Emissior rry® Smartphone model RI		Page 123(216)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	CW



0 dB = 184.9 V/m

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Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	CW

Date/Time: 26/08/2008 11:41:40 AM

Test Laboratory: RTS

File Name: HAC_E_GSM850_Mid_Chan.da4

DUT: BlackBerry Smartphone; Type: Sample; Serial: Not Specified

Program Name: HAC RF ER3D Device

Communication System: GSM 850; Frequency: 836.8 MHz; Duty Cycle: 1:8.3

Medium parameters used: s = 0 mho/m, $e_r = 1$; density = 1000 kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: ER3DV6 SN2285; ConvF(1, 1, 1); Calibrated: 07/03/2008
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 05/03/2008
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - ER3D - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 73.8 V/m; Power Drift = -0.081 dB

Maximum value of Total (measured) = 62.7 V/m

RTS RIM Testing Services		d Compatibility RF Emissio rry® Smartphone model R		Page 125(216)	
Author Data	Dates of Test	tes of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008 RTS-1191-0809-30 Rev 1 L6ARBW70CW		cw		

grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 192.9 V/m

Probe Modulation Factor = 3.07

Device Reference Point: 0.000, 0.000, 353.7 mm

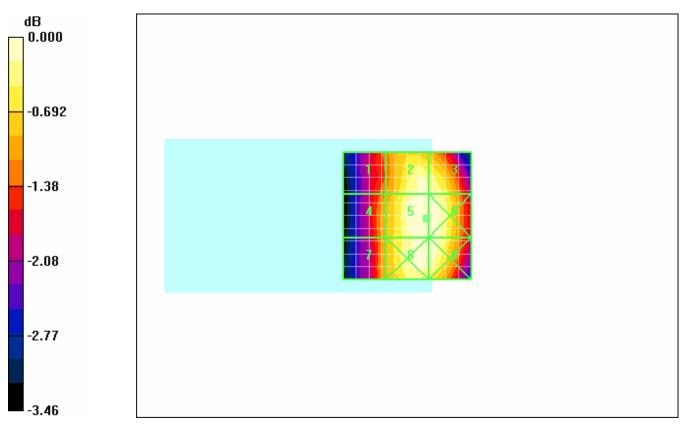
Reference Value = 73.8 V/m; Power Drift = -0.081 dB

Hearing Aid Near-Field Category: M3 (AWF -5 dB)

Peak E-field in V/m

Grid 1	Grid 2	Grid 3
169.6	189.5	189.3
\mathbf{M}	\mathbf{M}	\mathbf{M}
3	3	3
Grid 4	Grid 5	Grid 6
174.3	192.9	192.8
\mathbf{M}	\mathbf{M}	\mathbf{M}
3	3	3
Grid 7	Grid 8	Grid 9
174.1	192.3	192.3
\mathbf{M}	\mathbf{M}	\mathbf{M}
3	3	3

RTS RIM Testing Services		l Compatibility RF Emissio rry® Smartphone model RI		Page 126(216)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	Aug 26, Sep 26-27, 2008 RTS-1191-0809-30 Rev 1 L6ARBW70CW			CW



0 dB = 192.9V/m

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Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	cw

Date/Time: 26/08/2008 11:48:33 AM

Test Laboratory: RTS

File Name: HAC_E_GSM850_High_Chan.da4

DUT: BlackBerry Smartphone; Type: Sample; Serial: Not Specified

Program Name: HAC RF ER3D Device

Communication System: GSM 850; Frequency: 848.8 MHz; Duty Cycle: 1:8.3

Medium parameters used: s = 0 mho/m, $e_r = 1$; density = 1000 kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: ER3DV6 SN2285; ConvF(1, 1, 1); Calibrated: 07/03/2008
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 05/03/2008
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - ER3D - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 71.0 V/m; Power Drift = 0.061 dB

Maximum value of Total (measured) = 61.4 V/m

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Author Data	Dates of Test	tes of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008 RTS-1191-0809-30 Rev 1 L6ARBW70CW		\mathbf{cw}		

grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 188.8 V/m

Probe Modulation Factor = 3.07

Device Reference Point: 0.000, 0.000, 353.7 mm

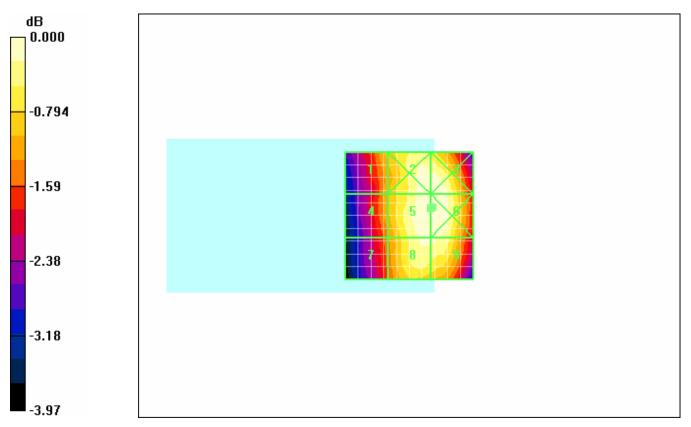
Reference Value = 71.0 V/m; Power Drift = 0.061 dB

Hearing Aid Near-Field Category: M3 (AWF -5 dB)

Peak E-field in V/m

Grid 1	Grid 2	Grid 3
169.7	188.0	188.0
\mathbf{M}	\mathbf{M}	\mathbf{M}
3	3	3
Grid 4	Grid 5	Grid 6
166.2	188.8	188.8
\mathbf{M}	\mathbf{M}	\mathbf{M}
3	3	3
Grid 7	Grid 8	Grid 9
161.2	185.0	184.6
M	\mathbf{M}	\mathbf{M}
3	3	3

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Daoud Attayi	Aug 26, Sep 26-27, 2008 RTS-1191-0809-30 Rev 1 L6ARBW70CW			CW



0 dB = 188.8V/m

RTS RIM Testing Services		d Compatibility RF Emission rry® Smartphone model RI		Page 130(216)
Author Data	Oates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	CW

Date/Time: 27/09/2008 9:59:10 AM

Test Laboratory: RTS

File Name: HAC_E_GSM850_Mid_Chan_Rev4.da4

DUT: BlackBerry Smartphone; Type: Sample; Serial: Not Specified

Program Name: HAC RF ER3D Device

Communication System: GSM 850; Frequency: 836.8 MHz; Duty Cycle: 1:8.3

Medium parameters used: s = 0 mho/m, $e_r = 1$; density = 1000 kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: ER3DV6 SN2285; ConvF(1, 1, 1); Calibrated: 07/03/2008
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 05/03/2008
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - ER3D - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 70.0 V/m; Power Drift = -0.015 dB

Maximum value of Total (measured) = 59.2 V/m

RTS RIM Testing Services	_	d Compatibility RF Emissio rry® Smartphone model R		Page 131(216)
Author Data	Pates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008 RTS-1191-0809-30 Rev 1 L6ARBW70CW			cw

grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 182.2 V/m

Probe Modulation Factor = 3.07

Device Reference Point: 0.000, 0.000, 353.7 mm

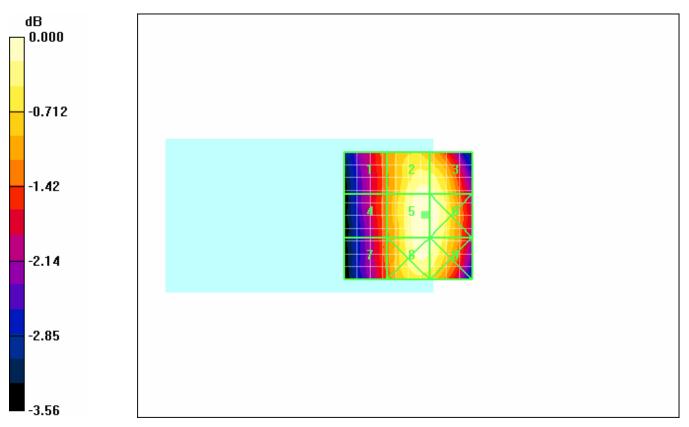
Reference Value = 70.0 V/m; Power Drift = -0.015 dB

Hearing Aid Near-Field Category: M3 (AWF -5 dB)

Peak E-field in V/m

Grid 1	Grid 2	Grid 3
159.0	179.8	178.9
M	\mathbf{M}	\mathbf{M}
3	3	3
Grid 4	Grid 5	Grid 6
159.4	182.2	181.5
M	\mathbf{M}	\mathbf{M}
3	3	3
Grid 7	Grid 8	Grid 9
157.6	180.5	179.7
M	\mathbf{M}	M
3	3	3

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Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008 RTS-1191-0809-30 Rev 1 L6ARBW70C			CW



0 dB = 182.2V/m

RTS RIM Testing Services	_	I Compatibility RF Emissio rry® Smartphone model R		Page 133(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	$\mathbf{c}\mathbf{w}$

Date/Time: 26/08/2008 4:52:22 PM

Test Laboratory: RTS

File Name: HAC_E_CDMA800_Low_Chan.da4

DUT: BlackBerry Smartphone; Type: Sample ; Serial: Not Specified

Program Name: HAC RF ER3D Device

Communication System: CDMA 800; Frequency: 824.7 MHz; Duty Cycle: 1:1

Medium parameters used: s = 0 mho/m, $e_r = 1$; density = 1000 kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: ER3DV6 SN2285; ConvF(1, 1, 1); Calibrated: 07/03/2008
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472: Calibrated: 05/03/2008
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8

Build 184

E Scan - ER3D - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 60.3 V/m; Power Drift = 0.088 dB

Maximum value of Total (measured) = 51.0 V/m

RTS RIM Testing Services		d Compatibility RF Emissio rry® Smartphone model R		Page 134(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70CW	

E Scan - ER3D - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Measurement

grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 48.0 V/m

Probe Modulation Factor = 0.940

Device Reference Point: 0.000, 0.000, 353.7 mm

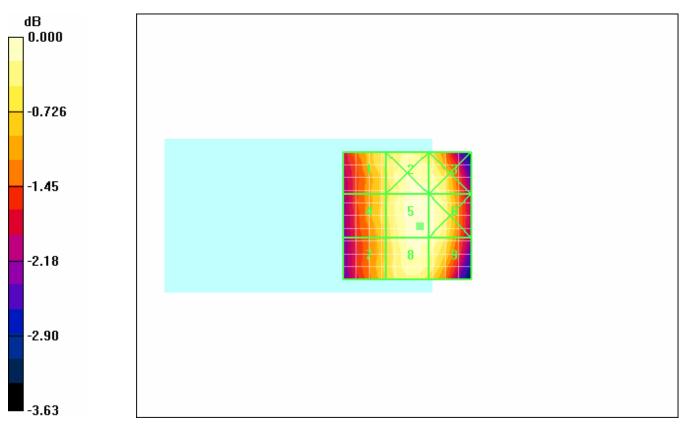
Reference Value = 60.3 V/m; Power Drift = 0.088 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak E-field in V/m

Grid 1	Grid 2	Grid 3
44.4	47.4	47.0
M	\mathbf{M}	M
4	4	4
Grid 4	Grid 5	Grid 6
43.8	48.0	47.4
M	M	M
4	4	4
Grid 7	Grid 8	Grid 9
43.2	47.2	46.8
M	M	M
4	4	4

RTS	Annex A to Hearing Aid Report for the BlackBe	Page 135(216)		
RIM Testing Services		133(210)		
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	CW



 $0\ dB = 48.0V/m$

RTS RIM Testing Services		d Compatibility RF Emission rry® Smartphone model RI		Page 136(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	CW

Date/Time: 26/08/2008 4:59:17 PM

Test Laboratory: RTS

File Name: HAC_E_CDMA800_Mid_Chan.da4

DUT: BlackBerry Smartphone; Type: Sample; Serial: Not Specified

Program Name: HAC RF ER3D Device

Communication System: CDMA 800; Frequency: 836.52 MHz; Duty Cycle: 1:1

Medium parameters used: s = 0 mho/m, $e_r = 1$; density = 1000 kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: ER3DV6 SN2285; ConvF(1, 1, 1); Calibrated: 07/03/2008
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 05/03/2008
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - ER3D - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 68.1 V/m; Power Drift = -0.033 dB

Maximum value of Total (measured) = 58.0 V/m

RTS RIM Testing Services	_	d Compatibility RF Emissio rry® Smartphone model R		Page 137(216)
Author Data	Dates of Test	ates of Test Report No FCC ID		
Daoud Attayi	Aug 26, Sep 26-27, 2008 RTS-1191-0809-30 Rev 1 L6ARBW70CW		cw	

grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 54.7 V/m

Probe Modulation Factor = 0.940

Device Reference Point: 0.000, 0.000, 353.7 mm

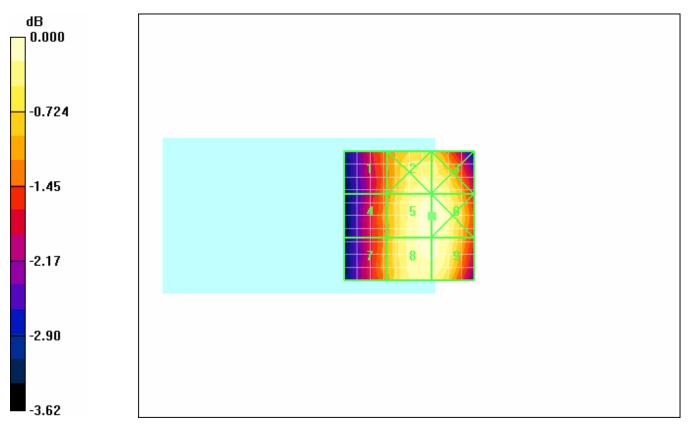
Reference Value = 68.1 V/m; Power Drift = -0.033 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak E-field in V/m

Grid 1	Grid 2	Grid 3
46.8	53.3	53.3
M	\mathbf{M}	${f M}$
4	4	4
Grid 4	Grid 5	Grid 6
47.6	54.7	54.7
\mathbf{M}	M	\mathbf{M}
4	4	4
Grid 7	Grid 8	Grid 9
47.8	54.0	53.8
\mathbf{M}	\mathbf{M}	${f M}$
4	4	4

RTS RIM Testing Services		d Compatibility RF Emission rry® Smartphone model RI		Page 138(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	CW



 $0\ dB = 54.7V/m$

RTS RIM Testing Services		d Compatibility RF Emission rry® Smartphone model RI		Page 139(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	CW

Date/Time: 26/08/2008 5:06:00 PM

Test Laboratory: RTS

File Name: HAC_E_CDMA800_High_Chan.da4

DUT: BlackBerry Smartphone; Type: Sample; Serial: Not Specified

Program Name: HAC RF ER3D Device

Communication System: CDMA 800; Frequency: 848.52 MHz; Duty Cycle: 1:1

Medium parameters used: s = 0 mho/m, $e_r = 1$; density = 1000 kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: ER3DV6 SN2285; ConvF(1, 1, 1); Calibrated: 07/03/2008
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 05/03/2008
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - ER3D - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 65.6 V/m; Power Drift = 0.056 dB

Maximum value of Total (measured) = 55.7 V/m

RTS RIM Testing Services		d Compatibility RF Emissio rry® Smartphone model R		Page 140(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70CW	

grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 52.5 V/m

Probe Modulation Factor = 0.940

Device Reference Point: 0.000, 0.000, 353.7 mm

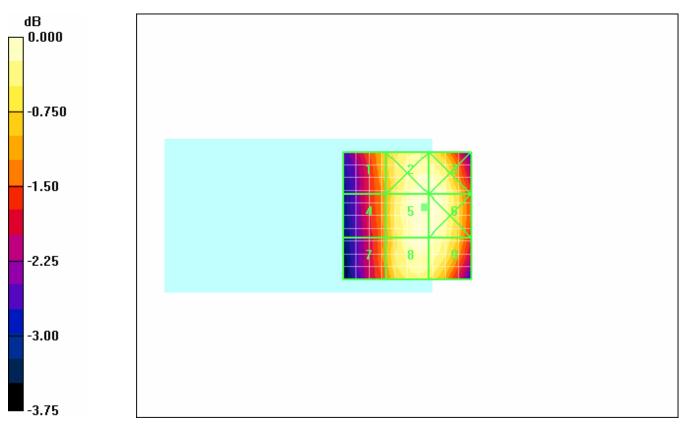
Reference Value = 65.6 V/m; Power Drift = 0.056 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak E-field in V/m

Grid 1	Grid 2	Grid 3
46.5	52.2	52.2
\mathbf{M}	M	\mathbf{M}
4	4	4
Grid 4	Grid 5	Grid 6
45.4	52.5	52.5
M	M	${f M}$
4	4	4
Grid 7	Grid 8	Grid 9
45.2	51.9	51.6
M	\mathbf{M}	${f M}$
4	4	4

RTS RIM Testing Services		I Compatibility RF Emissio rry® Smartphone model RI		Page 141(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	cw



0 dB = 52.5 V/m

RTS RIM Testing Services		d Compatibility RF Emission rry® Smartphone model RI		Page 142(216)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	CW

Date/Time: 26/08/2008 11:59:17 AM

Test Laboratory: RTS

File Name: HAC_E_GSM1900_Low_Chan.da4

DUT: BlackBerry Smartphone; Type: Sample; Serial: Not Specified

Program Name: HAC RF ER3D Device

Communication System: GSM 1900; Frequency: 1850.2 MHz; Duty Cycle: 1:8.3

Medium parameters used: s = 0 mho/m, $e_r = 1$; density = 1000 kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: ER3DV6 SN2285; ConvF(1, 1, 1); Calibrated: 07/03/2008
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 05/03/2008
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - ER3D - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 16.9 V/m: Power Drift = 0.129 dB

Maximum value of Total (measured) = 31.0 V/m

RTS RIM Testing Services	_	d Compatibility RF Emissio rry® Smartphone model R		Page 143(216)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	$\mathbf{c}\mathbf{w}$

grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 70.3 V/m

Probe Modulation Factor = 2.88

Device Reference Point: 0.000, 0.000, 353.7 mm

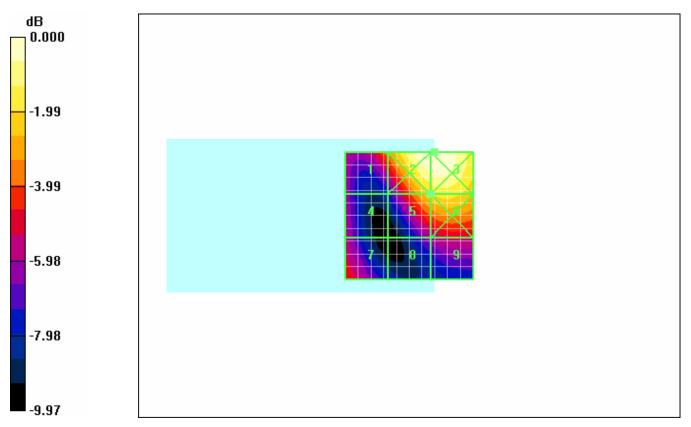
Reference Value = 16.9 V/m; Power Drift = 0.129 dB

Hearing Aid Near-Field Category: M3 (AWF -5 dB)

Peak E-field in V/m

0.114	0.110	0.110
Grid 1	Grid 2	Grid 3
60.2	88.9	89.2
M	\mathbf{M}	\mathbf{M}
3	2	2
Grid 4	Grid 5	Grid 6
46.5	70.3	73.4
M	M	M
4	3	3
Grid 7	Grid 8	Grid 9
52.9	44.8	49.6
M	M	\mathbf{M}
3	4	3

RTS RIM Testing Services	_	d Compatibility RF Emission rry® Smartphone model RI		Page 144(216)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	CW



0 dB = 89.2V/m

RTS RIM Testing Services		d Compatibility RF Emission rry® Smartphone model RI		Page 145(216)
Author Data	Dates of Test			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	CW

Date/Time: 26/08/2008 12:06:19 PM

Test Laboratory: RTS

File Name: HAC_E_GSM1900_Mid_Chan.da4

DUT: BlackBerry Smartphone; Type: Sample ; Serial: Not Specified

Program Name: HAC RF ER3D Device

Communication System: GSM 1900; Frequency: 1880 MHz; Duty Cycle: 1:8.3

Medium parameters used: s = 0 mho/m, $e_r = 1$; density = 1000 kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: ER3DV6 SN2285; ConvF(1, 1, 1); Calibrated: 07/03/2008
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 05/03/2008
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - ER3D - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 15.9 V/m; Power Drift = 0.151 dB

Maximum value of Total (measured) = 33.6 V/m

RTS RIM Testing Services		d Compatibility RF Emissio rry® Smartphone model R		Page 146(216)
Author Data	Dates of Test			
Daoud Attayi	Aug 26, Sep 26-27, 2008 RTS-1191-0809-30 Rev 1 L6ARBW70CV			cw

grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 74.4 V/m

Probe Modulation Factor = 2.88

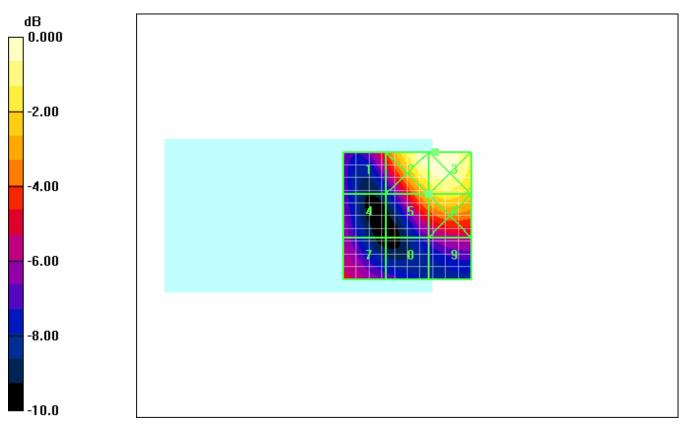
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 15.9 V/m; Power Drift = 0.151 dB

Peak E-field in V/m

Grid 1	Grid 2	Grid 3
60.0	95.9	96.7
\mathbf{M}	\mathbf{M}	\mathbf{M}
3	2	2
Grid 4	Grid 5	Grid 6
48.2	74.4	80.8
\mathbf{M}	M	${f M}$
3	3	3
Grid 7	Grid 8	Grid 9
54.1	44.9	51.0
M	\mathbf{M}	M
		3

RTS	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RBW71CW				
RIM Testing Services	147(2				
Author Data	Dates of Test				
Daoud Attayi	Aug 26, Sep 26-27, 2008 RTS-1191-0809-30 Rev 1 L6ARBW70CW			CW	



0 dB = 96.7 V/m

RTS RIM Testing Services		d Compatibility RF Emission rry® Smartphone model RI		Page 148(216)
Author Data	Dates of Test			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	CW

Date/Time: 27/09/2008 10:05:23 AM

Test Laboratory: RTS

File Name: HAC_E_GSM1900_Mid_Chan_Rev4.da4

DUT: BlackBerry Smartphone; Type: Sample; Serial: Not Specified Program Name: HAC RF ER3D Device

Communication System: GSM 1900; Frequency: 1880 MHz; Duty Cycle: 1:8.3

Medium parameters used: s = 0 mho/m, $e_r = 1$; density = 1000 kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: ER3DV6 SN2285; ConvF(1, 1, 1); Calibrated: 07/03/2008
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 05/03/2008
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - ER3D - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 18.5 V/m; Power Drift = -0.142 dB

Maximum value of Total (measured) = 32.8 V/m

RTS RIM Testing Services		d Compatibility RF Emissio rry® Smartphone model R		Page 149(216)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	Aug 26, Sep 26-27, 2008 RTS-1191-0809-30 Rev 1 L6ARBW70CW			cw

grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 76.2 V/m

Probe Modulation Factor = 2.88

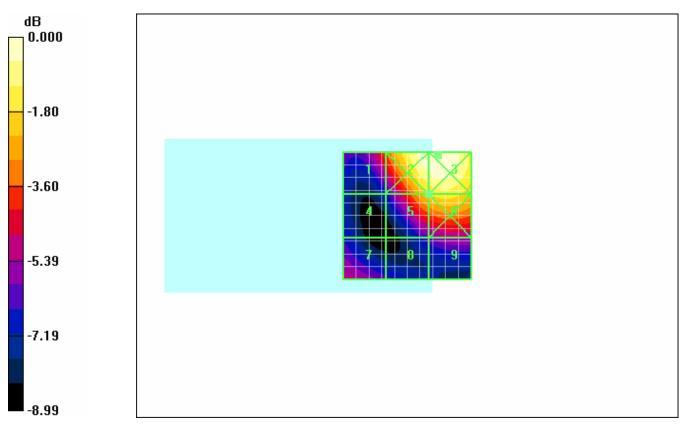
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 18.5 V/m; Power Drift = -0.142 dB

Peak E-field in V/m

Grid 1	Grid 2	Grid 3
62.4	93.6	94.8
M	\mathbf{M}	\mathbf{M}
3	2	2
Grid 4	Grid 5	Grid 6
44.3	76.2	80.2
M	\mathbf{M}	${f M}$
4	3	3
Grid 7	Grid 8	Grid 9
53.4	47.4	51.7
M	M	${f M}$
3	3	3

RTS RIM Testing Services		d Compatibility RF Emission rry® Smartphone model RI		Page 150(216)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	CW



 $0\ dB = 94.8V/m$

RTS RIM Testing Services		d Compatibility RF Emission rry® Smartphone model RI		Page 151(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	CW

Date/Time: 26/08/2008 12:13:27 PM

Test Laboratory: RTS

File Name: HAC_E_GSM1900_High_Chan.da4

DUT: BlackBerry Smartphone; Type: Sample; Serial: Not Specified

Program Name: HAC RF ER3D Device

Communication System: GSM 1900; Frequency: 1909.8 MHz; Duty Cycle: 1:8.3

Medium parameters used: s = 0 mho/m, $e_r = 1$; density = 1000 kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: ER3DV6 SN2285; ConvF(1, 1, 1); Calibrated: 07/03/2008
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 05/03/2008
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - ER3D - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 15.6 V/m; Power Drift = -0.010 dB

Maximum value of Total (measured) = 31.4 V/m

RTS RIM Testing Services		d Compatibility RF Emissio rry® Smartphone model R		Page 152(216)
Author Data	Dates of Test			
Daoud Attayi	Aug 26, Sep 26-27, 2008 RTS-1191-0809-30 Rev 1 L6ARBW70C			cw

grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 69.1 V/m

Probe Modulation Factor = 2.88

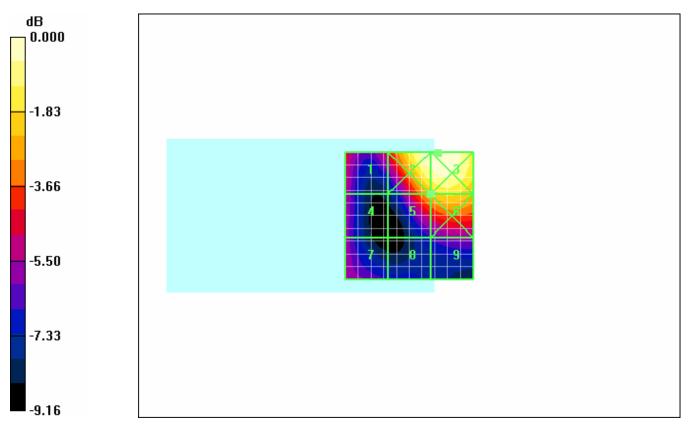
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 15.6 V/m; Power Drift = -0.010 dB

Peak E-field in V/m

Grid 1	Grid 2	Grid 3
55.2	89.6	90.7
N	1 N	\mathbf{M}
3	2	2
Grid 4	Grid 5	Grid 6
49.7	69.1	74.8
N	1 N	1 M
3	2	2
3	3	3
Grid 7	Grid 8	Grid 9
Grid 7	Grid 8 42.5	Grid 9 46.9

RTS RIM Testing Services		d Compatibility RF Emission rry® Smartphone model RI		Page 153(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	CW



0 dB = 90.7V/m

RTS RIM Testing Services		l Compatibility RF Emissio rry® Smartphone model R		Page 154(216)	
Author Data	ates of Test Report No FCC ID				
Daoud Attayi	Aug 26, Sep 26-27, 2008 RTS-1191-0809-30 Rev 1 L6ARBW70CW			CW	

Date/Time: 26/08/2008 4:27:23 PM

Test Laboratory: RTS

File Name: HAC_E_CDMA1900_Low_Chan.da4

DUT: BlackBerry Smartphone; Type: Sample; Serial: Not Specified

Program Name: HAC RF ER3D Device

Communication System: CDMA 1900; Frequency: 1851.25 MHz; Duty Cycle: 1:1

Medium parameters used: s = 0 mho/m, $e_r = 1$; density = 1000 kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: ER3DV6 SN2285; ConvF(1, 1, 1); Calibrated: 07/03/2008
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 05/03/2008
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - ER3D - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 23.6 V/m; Power Drift = 0.057 dB

Maximum value of Total (measured) = 42.0 V/m

RTS RIM Testing Services	_	d Compatibility RF Emissio rry® Smartphone model R		Page 155(216)
Author Data	Dates of Test			
Daoud Attayi	Aug 26, Sep 26-27, 2008	Aug 26, Sep 26-27, 2008 RTS-1191-0809-30 Rev 1 L6ARBW70C		

grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 28.9 V/m

Probe Modulation Factor = 0.870

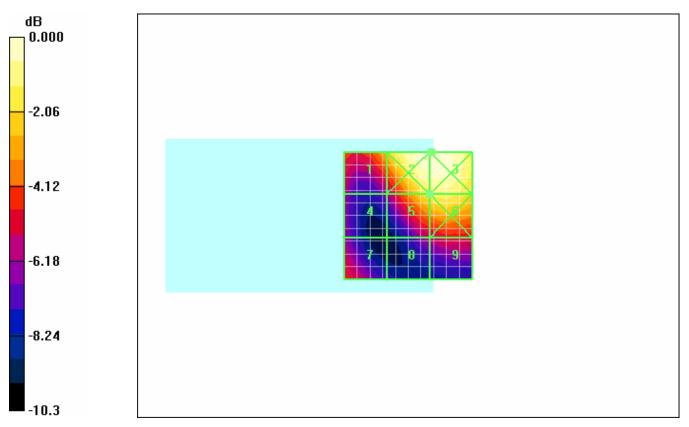
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 23.6 V/m; Power Drift = 0.057 dB

Peak E-field in V/m

Grid 1	Grid 2	Grid 3
25.8	36.6	36.6
M	\mathbf{M}	M
4	4	4
Grid 4	Grid 5	Grid 6
17.1	28.9	30.1
M	M	\mathbf{M}
4	4	4
Grid 7	Grid 8	Grid 9
20.3	17.7	19.4
M	M	\mathbf{M}
4	4	4

RTS RIM Testing Services		l Compatibility RF Emissior rry® Smartphone model RI		Page 156(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	CW



0 dB = 36.6V/m

RTS RIM Testing Services		d Compatibility RF Emission rry® Smartphone model RI		Page 157(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008 RTS-1191-0809-30 Rev 1 L6ARBW70CW		CW	

Date/Time: 26/08/2008 4:34:44 PM

Test Laboratory: RTS

File Name: HAC_E_CDMA1900_Mid_Chan.da4

DUT: BlackBerry Smartphone; Type: Sample; Serial: Not Specified

Program Name: HAC RF ER3D Device

Communication System: CDMA 1900; Frequency: 1880 MHz; Duty Cycle: 1:1

Medium parameters used: s = 0 mho/m, $e_r = 1$; density = 1000 kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: ER3DV6 SN2285; ConvF(1, 1, 1); Calibrated: 07/03/2008
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 05/03/2008
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - ER3D - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 22.9 V/m; Power Drift = 0.180 dB

Maximum value of Total (measured) = 48.0 V/m

RTS RIM Testing Services		I Compatibility RF Emission rry® Smartphone model RI		Page 158(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008 RTS-1191-0809-30 Rev 1 L6ARBW70CW			CW

grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 31.9 V/m

Probe Modulation Factor = 0.870

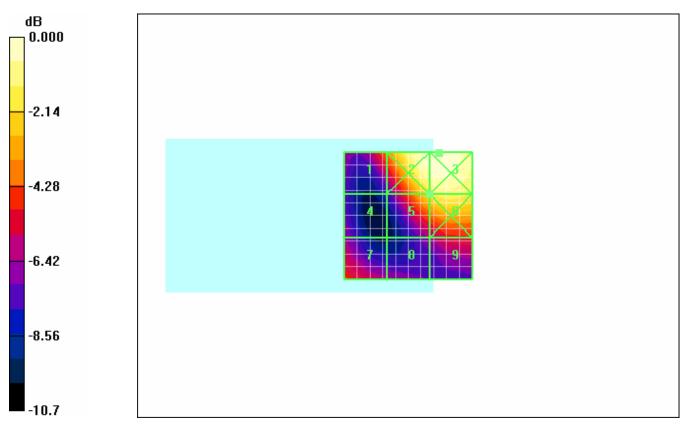
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 22.9 V/m; Power Drift = 0.180 dB

Peak E-field in V/m

Grid 1	Grid 2	Grid 3
25.7	41.2	42.1
M	\mathbf{M}	M
4	4	4
Grid 4	Grid 5	Grid 6
18.7	31.9	34.5
M	\mathbf{M}	M
4	4	4
Grid 7	Grid 8	Grid 9
22.9	19.2	22.3
M	\mathbf{M}	\mathbf{M}
4	4	4

RTS RIM Testing Services		d Compatibility RF Emission rry® Smartphone model RI		Page 159(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008 RTS-1191-0809-30 Rev 1 L6ARBW70CW			CW



0 dB = 42.1 V/m

RTS RIM Testing Services	_	d Compatibility RF Emission rry® Smartphone model RI		Page 160(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008 RTS-1191-0809-30 Rev 1 L6ARBW70CW			CW

Date/Time: 26/08/2008 4:42:38 PM

Test Laboratory: RTS

File Name: HAC_E_CDMA1900_High_Chan.da4

DUT: BlackBerry Smartphone; Type: Sample; Serial: Not Specified

Program Name: HAC RF ER3D Device

Communication System: CDMA 1900; Frequency: 1908.5 MHz; Duty Cycle: 1:1

Medium parameters used: s = 0 mho/m, $e_r = 1$; density = 1000 kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: ER3DV6 SN2285; ConvF(1, 1, 1); Calibrated: 07/03/2008
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 05/03/2008
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - ER3D - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 23.2 V/m; Power Drift = 0.320 dB

Maximum value of Total (measured) = 44.5 V/m

RTS RIM Testing Services		d Compatibility RF Emissio rry® Smartphone model R		Page 161(216)
Author Data	Dates of Test			
Daoud Attayi	Aug 26, Sep 26-27, 2008	ug 26, Sep 26-27, 2008 RTS-1191-0809-30 Rev 1 L6ARBW70CW		

grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 30.3 V/m

Probe Modulation Factor = 0.870

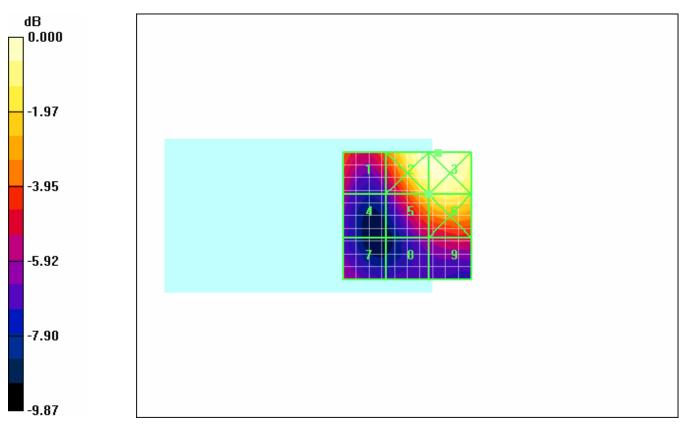
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 23.2 V/m; Power Drift = 0.320 dB

Peak E-field in V/m

Grid 1	Grid 2	Grid 3
23.8	38.4	38.9
\mathbf{M}	M	\mathbf{M}
4	4	4
Grid 4	Grid 5	Grid 6
18.8	30.3	32.6
\mathbf{M}	M	M
4	4	4
Grid 7	Grid 8	Grid 9
18.9	18.9	21.0
\mathbf{N}	M	M
1	1	4

RTS RIM Testing Services		d Compatibility RF Emission rry® Smartphone model RI		Page 162(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008 RTS-1191-0809-30 Rev 1 L6ARBW70C			CW



0 dB = 38.9V/m

RTS RIM Testing Services		d Compatibility RF Emission rry® Smartphone model RI		Page 163(216)
Author Data	Dates of Test	Dates of Test Report No FCC ID		
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	cw

Date/Time: 29/07/2008 6:31:43 PM

Test Laboratory: RTS

File Name: HAC_H_GSM850_Low_Chan.da4

DUT: BlackBerry Smartphone; Type: Sample ; Serial: Not Specified

Program Name: HAC RF H3DV6 Device

Communication System: GSM 850; Frequency: 824.2 MHz; Duty Cycle: 1:8.3

Medium parameters used: s = 0 mho/m, $e_r = 1$; density = 1 kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: H3DV6 SN6105; ; Calibrated: 09/11/2007
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 05/03/2008
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.072 A/m: Power Drift = 0.136 dB

Maximum value of Total (measured) = 0.140 A/m

RTS RIM Testing Services		d Compatibility RF Emissio rry® Smartphone model R		Page 164(216)	
Author Data	Dates of Test	rates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008 RTS-1191-0809-30 Rev 1 L6ARBW70CW		cw		

grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.353 A/m

Probe Modulation Factor = 2.64

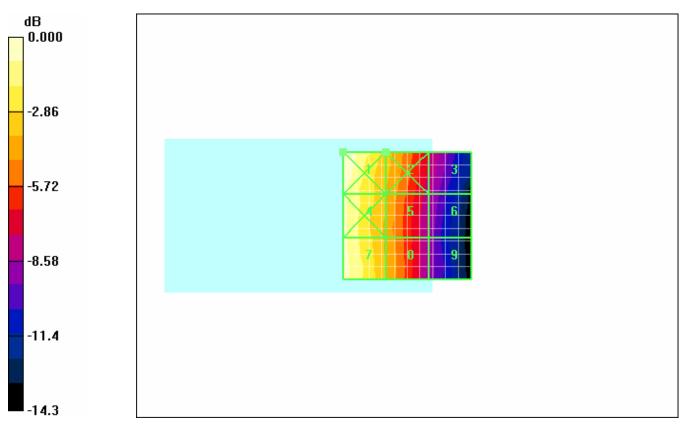
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.072 A/m; Power Drift = 0.136 dB

Peak H-field in A/m

Grid 1	Grid 2	Grid 3
0.370	0.254	0.158
M	M	M
4	4	4
Grid 4	Grid 5	Grid 6
0.347	0.240	0.143
\mathbf{M}	M	\mathbf{M}
4	4	4
Grid 7	Grid 8	Grid 9
0.353	0.240	0.134
M	\mathbf{M}	\mathbf{M}
4	4	4

RTS RIM Testing Services		I Compatibility RF Emissio rry® Smartphone model RI		Page 165(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70CW	



0 dB = 0.370 A/m

RTS RIM Testing Services		d Compatibility RF Emission rry® Smartphone model RI		Page 166(216)
Author Data	Dates of Test	Oates of Test Report No FCC ID		
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	CW

Date/Time: 26/08/2008 1:59:35 PM

Test Laboratory: RTS

File Name: HAC_H_GSM850_Mid_Chan.da4

DUT: BlackBerry Smartphone; Type: Sample; Serial: Not Specified

Program Name: HAC RF H3DV6 Device

Communication System: GSM 850; Frequency: 836.8 MHz; Duty Cycle: 1:8.3

Medium parameters used: s = 0 mho/m, $e_r = 1$; density = 1 kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: H3DV6 SN6105; ; Calibrated: 09/11/2007
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 05/03/2008
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.088 A/m: Power Drift = 0.037 dB

Maximum value of Total (measured) = 0.147 A/m

RTS RIM Testing Services		d Compatibility RF Emissio rry® Smartphone model R		Page 167(216)	
Author Data	Dates of Test	Pates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008 RTS-1191-0809-30 Rev 1 L6ARBW70CW		\mathbf{cw}		

grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.350 A/m

Probe Modulation Factor = 2.64

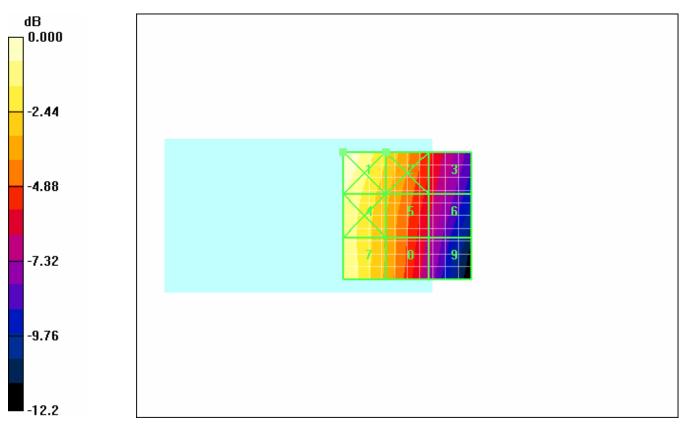
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.088 A/m; Power Drift = 0.037 dB

Peak H-field in A/m

Grid 1	Grid 2	Grid 3
0.387	0.296	0.208
M	\mathbf{M}	M
4	4	4
Grid 4	Grid 5	Grid 6
0.358	0.275	0.194
\mathbf{M}	\mathbf{M}	\mathbf{M}
4	4	4
Grid 7	Grid 8	Grid 9
0.350	0.264	0.178
M	\mathbf{M}	\mathbf{M}
4	4	4

RTS RIM Testing Services		d Compatibility RF Emissio rry® Smartphone model R		Page 168(216)	
Author Data	Dates of Test	ates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70CW		



0 dB = 0.387 A/m

RTS RIM Testing Services		d Compatibility RF Emission rry® Smartphone model RI		Page 169(216)
Author Data	Dates of Test	Oates of Test Report No FCC ID		
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	CW

Date/Time: 26/08/2008 2:08:13 PM

Test Laboratory: RTS

File Name: HAC_H_GSM850_High_Chan.da4

DUT: BlackBerry Smartphone; Type: Sample; Serial: Not Specified

Program Name: HAC RF H3DV6 Device

Communication System: GSM 850; Frequency: 848.8 MHz; Duty Cycle: 1:8.3

Medium parameters used: s = 0 mho/m, $e_r = 1$; density = 1 kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: H3DV6 SN6105; ; Calibrated: 09/11/2007
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 05/03/2008
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.094 A/m: Power Drift = 0.015 dB

Maximum value of Total (measured) = 0.149 A/m

RTS RIM Testing Services		d Compatibility RF Emissio rry® Smartphone model R		Page 170(216)	
Author Data	Dates of Test	ates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008 RTS-1191-0809-30 Rev 1 L6ARBW70CW		cw		

grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.377 A/m

Probe Modulation Factor = 2.64

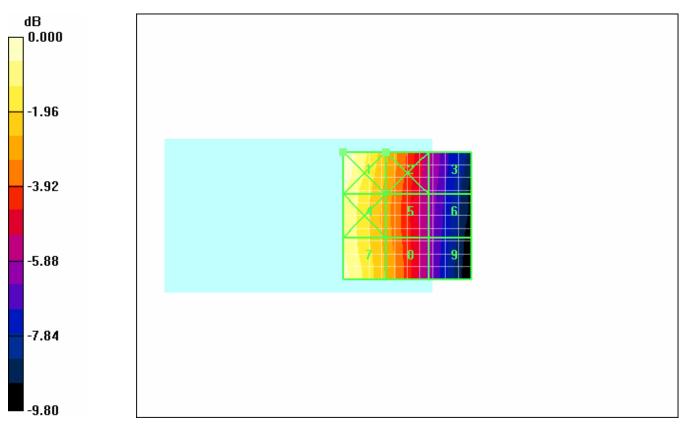
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.094 A/m; Power Drift = 0.015 dB

Peak H-field in A/m

Grid 1 0.395	Grid 2 0.298	Grid 3 0.208
M	M	M
Grid 4	Grid 5	4 Grid 6
0.369 M	0.286 M	0.200 M
4	4	4
Grid 7	Grid 8	Grid 9
0.377	0.291	0.197
M	\mathbf{M}	M
4	4	4

RTS	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RBW71CW				
RIM Testing Services					
Author Data	Dates of Test Report No FCC ID				
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70CW		



0 dB = 0.395 A/m

RTS RIM Testing Services		d Compatibility RF Emission rry® Smartphone model RI		Page 172(216)
Author Data	Dates of Test	Dates of Test Report No FCC ID		
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	CW

Date/Time: 27/09/2008 10:51:14 AM

Test Laboratory: RTS

File Name: HAC_H_GSM850_High_Chan_Rev4.da4

DUT: BlackBerry Smartphone; Type: Sample ; Serial: Not Specified Program Name: HAC RF H3DV6 Device

Communication System: GSM 850; Frequency: 848.8 MHz; Duty Cycle: 1:8.3

Medium parameters used: s = 0 mho/m, $e_r = 1$; density = 1 kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: H3DV6 SN6105; ; Calibrated: 09/11/2007
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 05/03/2008
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.088 A/m: Power Drift = 0.076 dB

Maximum value of Total (measured) = 0.141 A/m

RTS RIM Testing Services		d Compatibility RF Emissio rry® Smartphone model R		Page 173(216)	
Author Data	Dates of Test	ates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008 RTS-1191-0809-30 Rev 1 L6ARBW70CW			cw	

grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.371 A/m

Probe Modulation Factor = 2.64

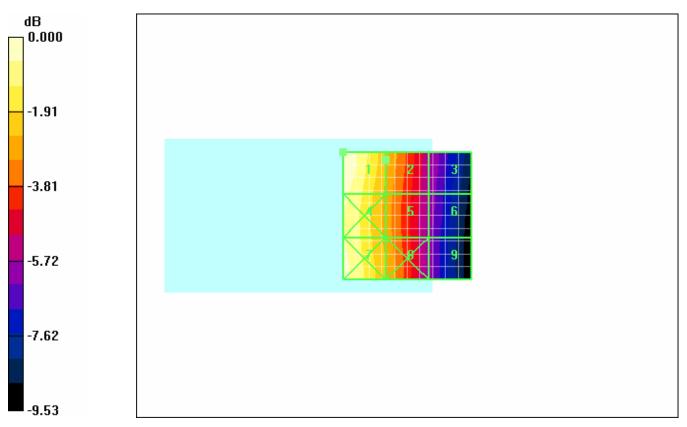
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.088 A/m; Power Drift = 0.076 dB

Peak H-field in A/m

Grid 1	Grid 2	Grid 3
0.371	0.282	0.196
M	\mathbf{M}	M
4	4	4
Grid 4	Grid 5	Grid 6
0.352	0.273	0.191
\mathbf{M}	M	\mathbf{M}
4	4	4
Grid 7	Grid 8	Grid 9
0.353	0.278	0.187
\mathbf{M}	\mathbf{M}	M
4	4	4

RTS RIM Testing Services		d Compatibility RF Emission rry® Smartphone model R		Page 174(216)	
Author Data	Dates of Test	ates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW700	$\mathbf{c}\mathbf{w}$	



0 dB = 0.371 A/m

RTS RIM Testing Services	_	I Compatibility RF Emissio rry® Smartphone model R		Page 175(216)	
Author Data	Dates of Test	ates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	CW	

Date/Time: 26/08/2008 3:33:07 PM

Test Laboratory: RTS

File Name: HAC_H_CDMA800_Low_Chan.da4

DUT: BlackBerry Smartphone; Type: Sample; Serial: Not Specified

Program Name: HAC RF H3DV6 Device

Communication System: CDMA 800; Frequency: 824.7 MHz; Duty Cycle: 1:1

Medium parameters used: s = 0 mho/m, $e_r = 1$; density = 1 kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 09/11/2007

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472: Calibrated: 05/03/2008

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8

Build 184

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.070 A/m; Power Drift = 0.030 dB

Maximum value of Total (measured) = 0.124 A/m

RTS RIM Testing Services		I Compatibility RF Emissio rry® Smartphone model RI		Page 176(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008 RTS-1191-0809-30 Rev 1 L6ARBW70CW		CW	

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Measurement

grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.108 A/m

Probe Modulation Factor = 0.970

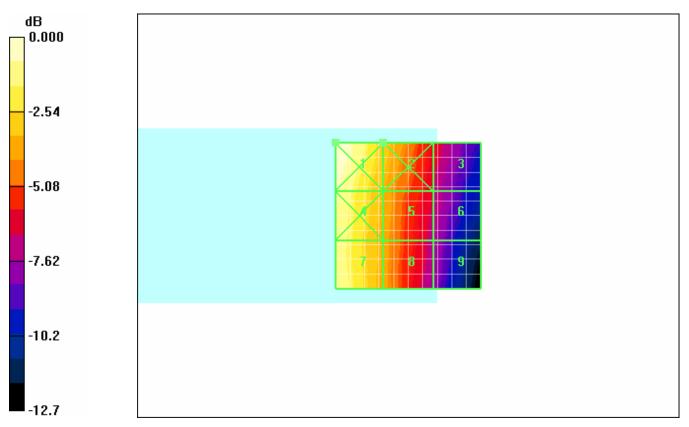
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.070 A/m; Power Drift = 0.030 dB

Peak H-field in A/m

Grid 1 0.120	Grid 2 0.085	Grid 3 0.059
M	\mathbf{M}	M
4	4	4
Grid 4	Grid 5	Grid 6
0.110	0.080	0.055
M	\mathbf{M}	\mathbf{M}
4	4	4
Grid 7	Grid 8	Grid 9
0.108	0.078	0.051
M	\mathbf{M}	\mathbf{M}
4	4	4

RTS RIM Testing Services	Annex A to Hearing Aid Report for the BlackBe	Page 177(216)				
Author Data	Dates of Test	Dates of Test Report No FCC ID				
Daoud Attayi	Aug 26, Sep 26-27, 2008 RTS-1191-0809-30 Rev 1 L6ARBW70CW		CW			



0 dB = 0.120 A/m

RTS RIM Testing Services		d Compatibility RF Emission rry® Smartphone model RI		Page 178(216)
Author Data	Dates of Test	Dates of Test Report No FCC ID		
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	CW

Date/Time: 26/08/2008 3:40:49 PM

Test Laboratory: RTS

File Name: HAC_H_CDMA800_Mid_Chan.da4

DUT: BlackBerry Smartphone; Type: Sample; Serial: Not Specified

Program Name: HAC RF H3DV6 Device

Communication System: CDMA 800; Frequency: 824.7 MHz; Duty Cycle: 1:1

Medium parameters used: s = 0 mho/m, $e_r = 1$; density = 1 kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: H3DV6 SN6105; ; Calibrated: 09/11/2007
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 05/03/2008
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.085 A/m; Power Drift = -0.044 dB

Maximum value of Total (measured) = 0.138 A/m

RTS RIM Testing Services		d Compatibility RF Emissio rry® Smartphone model R		Page 179(216)	
Author Data	Dates of Test	ates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008 RTS-1191-0809-30 Rev 1 L6ARBW70CW		\mathbf{cw}		

grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.122 A/m

Probe Modulation Factor = 0.970

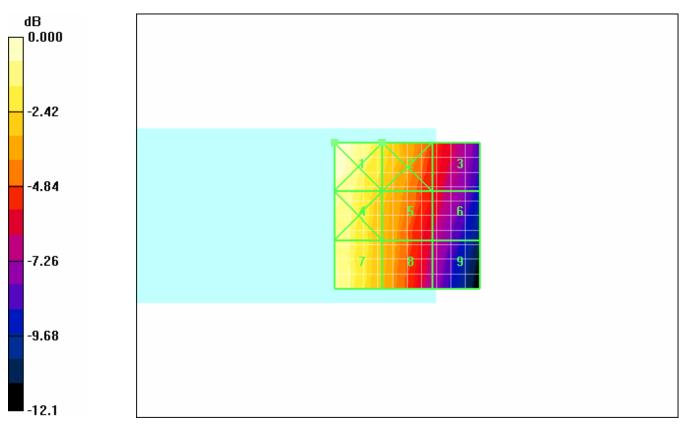
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.085 A/m; Power Drift = -0.044 dB

Peak H-field in A/m

Grid 1	Grid 2	Grid 3
0.134	0.104	0.075
M	\mathbf{M}	M
4	4	4
Grid 4	Grid 5	Grid 6
0.122	0.096	0.069
\mathbf{M}	M	\mathbf{M}
4	4	4
Grid 7	Grid 8	Grid 9
0.122	0.093	0.063
M	\mathbf{M}	M
4	4	4

RTS RIM Testing Services		d Compatibility RF Emissio rry® Smartphone model R		Page 180(216)	
Author Data	Dates of Test	tes of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008 RTS-1191-0809-30 Rev 1 L6ARBW70CW		cw		



0 dB = 0.134A/m

RTS RIM Testing Services		d Compatibility RF Emission rry® Smartphone model RI		Page 181(216)	
Author Data	Dates of Test	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	cw	

Date/Time: 26/08/2008 3:48:23 PM

Test Laboratory: RTS

File Name: HAC_H_CDMA800_High_Chan.da4

DUT: BlackBerry Smartphone; Type: Sample ; Serial: Not Specified Program Name: HAC RF H3DV6 Device

Communication System: CDMA 800; Frequency: 848.52 MHz; Duty Cycle: 1:1

Medium parameters used: s = 0 mho/m, $e_r = 1$; density = 1 kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: H3DV6 SN6105; ; Calibrated: 09/11/2007
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 05/03/2008
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.083 A/m: Power Drift = -0.157 dB

Maximum value of Total (measured) = 0.135 A/m

RTS RIM Testing Services		d Compatibility RF Emission		Page 182(216)	
Author Data	Dates of Test	Dates of Test Report No FCC ID			
Daoud Attavi	Aug 26, Sep 26-27, 2008 RTS-1191-0809-30 Rev 1 L6ARBW70CV		cw		

grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.127 A/m

Probe Modulation Factor = 0.970

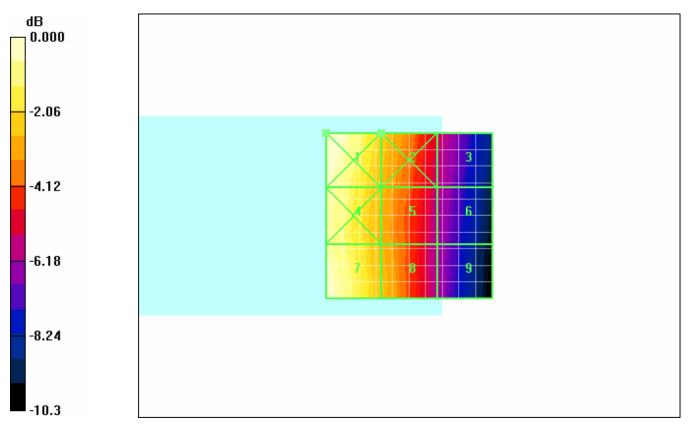
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.083 A/m; Power Drift = -0.157 dB

Peak H-field in A/m

Grid 1	Grid 2	Grid 3
0.131	0.101	0.070
\mathbf{M}	\mathbf{M}	M
4	4	4
Grid 4	Grid 5	Grid 6
0.122	0.096	0.067
\mathbf{M}	M	\mathbf{M}
4	4	4
Grid 7	Grid 8	Grid 9
0.127	0.097	0.064
\mathbf{M}	\mathbf{M}	M
4	4	4

RTS RIM Testing Services		d Compatibility RF Emission rry® Smartphone model RI		Page 183(216)
Author Data	Dates of Test	Dates of Test Report No FCC ID		
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	CW



0 dB = 0.131A/m

RTS RIM Testing Services		d Compatibility RF Emission		Page 184(216)	
Author Data	Dates of Test	ates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	cw	

Date/Time: 26/08/2008 2:17:29 PM

Test Laboratory: RTS

File Name: HAC_H_GSM1900_Low_Chan.da4

DUT: BlackBerry Smartphone; Type: Sample ; Serial: Not Specified

Program Name: HAC RF H3DV6 Device

Communication System: GSM 1900; Frequency: 1850.2 MHz; Duty Cycle: 1:8.3

Medium parameters used: s = 0 mho/m, $e_r = 1$; density = 1 kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: H3DV6 SN6105; ; Calibrated: 09/11/2007
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 05/03/2008
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.070 A/m; Power Drift = 0.029 dB

Maximum value of Total (measured) = 0.110 A/m

RTS RIM Testing Services	_	d Compatibility RF Emissio rry® Smartphone model R		Page 185(216)
Author Data	Dates of Test	Dates of Test Report No FCC ID		
Daoud Attayi	Aug 26, Sep 26-27, 2008 RTS-1191-0809-30 Rev 1 L6ARBW70CW			cw

grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.198 A/m

Probe Modulation Factor = 2.53

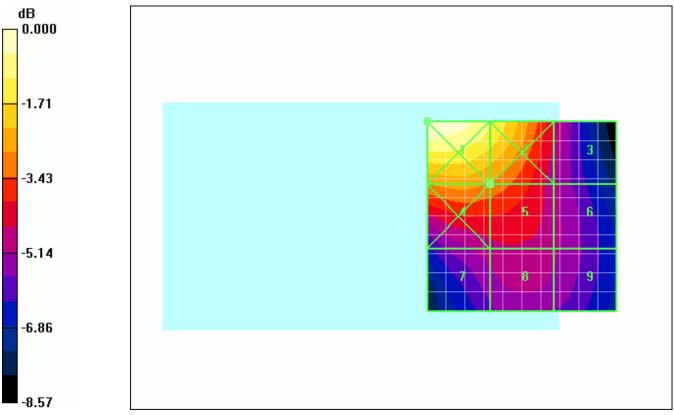
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.070 A/m; Power Drift = 0.029 dB

Peak H-field in A/m

Grid 1	Grid 2	Grid 3
0.277	0.245	0.165
M	\mathbf{M}	M
2	3	3
Grid 4	Grid 5	Grid 6
0.205	0.198	0.158
\mathbf{M}	\mathbf{M}	\mathbf{M}
3	3	3
Grid 7	Grid 8	Grid 9
0.160	0.163	0.156
\mathbf{M}	\mathbf{M}	\mathbf{M}
3	3	3

RTS RIM Testing Services		d Compatibility RF Emission rry® Smartphone model RI		Page 186(216)
Author Data	Dates of Test	Dates of Test Report No FCC ID		
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	CW



0 dB = 0.277 A/m

RTS RIM Testing Services		d Compatibility RF Emission rry® Smartphone model RI		Page 187(216)
Author Data	Dates of Test	Dates of Test Report No FCC ID		
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	CW

Date/Time: 26/08/2008 2:25:07 PM

Test Laboratory: RTS

File Name: HAC_H_GSM1900_Mid_Chan.da4

DUT: BlackBerry Smartphone; Type: Sample; Serial: Not Specified Program Name: HAC RF H3DV6 Device

Communication System: GSM 1900; Frequency: 1880 MHz; Duty Cycle: 1:8.3

Medium parameters used: s = 0 mho/m, $e_r = 1$; density = 1 kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: H3DV6 SN6105; ; Calibrated: 09/11/2007
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 05/03/2008
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.070 A/m; Power Drift = -0.017 dB

Maximum value of Total (measured) = 0.108 A/m

RTS RIM Testing Services		d Compatibility RF Emissio rry® Smartphone model R		Page 188(216)	
Author Data	Dates of Test	tes of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	91-0809-30 Rev 1 L6ARBW70CW		

grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.195 A/m

Probe Modulation Factor = 2.53

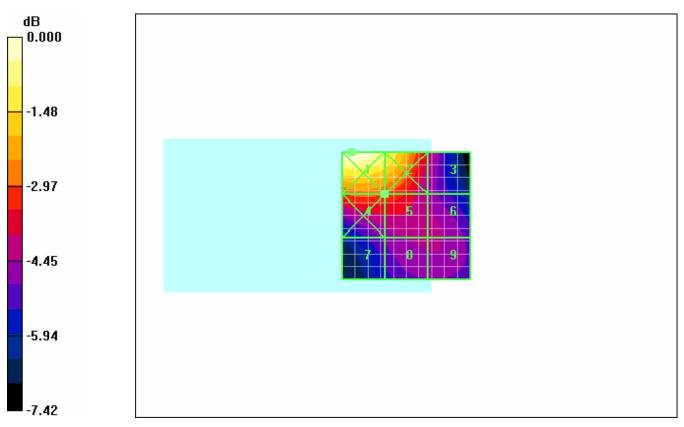
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.070 A/m; Power Drift = -0.017 dB

Peak H-field in A/m

Grid 1	Grid 2	Grid 3
0.273	0.249	0.176
M	\mathbf{M}	M
2	3	3
Grid 4	Grid 5	Grid 6
0.199	0.195	0.167
\mathbf{M}	\mathbf{M}	\mathbf{M}
3	3	3
Grid 7	Grid 8	Grid 9
0.158	0.166	0.166
M	\mathbf{M}	\mathbf{M}
3	3	3

RTS RIM Testing Services		l Compatibility RF Emission rry® Smartphone model RI		Page 189(216)
Author Data	Dates of Test			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70CW	



0 dB = 0.273 A/m

RTS RIM Testing Services	_	l Compatibility RF Emissio rry® Smartphone model R		Page 190(216)	
Author Data	Dates of Test	ates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70CW		

Date/Time: 27/09/2008 10:59:01 AM

Test Laboratory: RTS

File Name: HAC_H_GSM1900_Mid_Chan_Rev4.da4

DUT: BlackBerry Smartphone; Type: Sample; Serial: Not Specified Program Name: HAC RF H3DV6 Device

Communication System: GSM 1900; Frequency: 1880 MHz; Duty Cycle: 1:8.3

Medium parameters used: s = 0 mho/m, $e_r = 1$; density = 1 kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: H3DV6 SN6105; ; Calibrated: 09/11/2007
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 05/03/2008
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.068 A/m; Power Drift = 0.114 dB

Maximum value of Total (measured) = 0.101 A/m

RTS RIM Testing Services		d Compatibility RF Emissio rry® Smartphone model R		Page 191(216)	
Author Data	Dates of Test	ates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008 RTS-1191-0809-30 Rev 1 L6ARBW70CW			$\mathbf{c}\mathbf{w}$	

grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.191 A/m

Probe Modulation Factor = 2.53

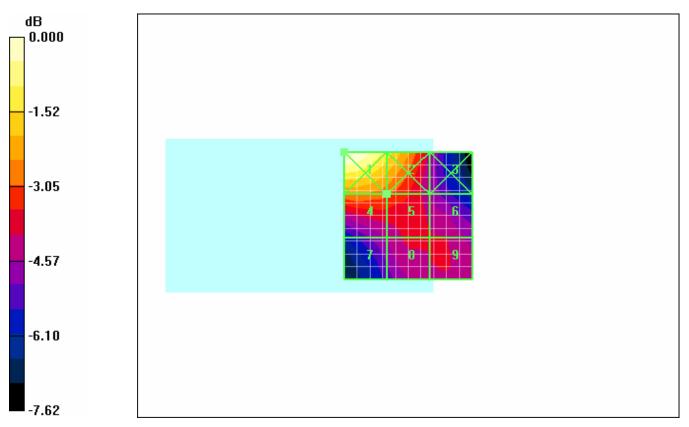
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.068 A/m; Power Drift = 0.114 dB

Peak H-field in A/m

Grid 1 0.255	Grid 2 0.222	Grid 3 0.156
M	\mathbf{M}	M
2	3	3
Grid 4	Grid 5	Grid 6
0.191	0.182	0.161
\mathbf{M}	M	\mathbf{M}
3	3	3
Grid 7	Grid 8	Grid 9
0.152	0.164	0.162
M	\mathbf{M}	\mathbf{M}
3	3	3

RTS RIM Testing Services		d Compatibility RF Emission rry® Smartphone model RI		Page 192(216)
Author Data	Dates of Test			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70CW	



0 dB = 0.255 A/m

RTS RIM Testing Services		d Compatibility RF Emission		Page 193(216)	
Author Data	Dates of Test	ates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	$\mathbf{c}\mathbf{w}$	

Date/Time: 26/08/2008 2:37:10 PM

Test Laboratory: RTS

File Name: HAC_H_GSM1900_High_Chan.da4

DUT: BlackBerry Smartphone; Type: Sample; Serial: Not Specified Program Name: HAC RF H3DV6 Device

Communication System: GSM 1900; Frequency: 1909.8 MHz; Duty Cycle: 1:8.3

Medium parameters used: s = 0 mho/m, $e_r = 1$; density = 1 kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: H3DV6 SN6105; ; Calibrated: 09/11/2007
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 05/03/2008
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.066 A/m: Power Drift = -0.146 dB

Maximum value of Total (measured) = 0.106 A/m

RTS RIM Testing Services		d Compatibility RF Emissio rry® Smartphone model R		Page 194(216)		
Author Data	Dates of Test	tes of Test Report No FCC ID				
Daoud Attayi	Aug 26, Sep 26-27, 2008 RTS-1191-0809-30 Rev 1 L6ARBW70CW			$\mathbf{c}\mathbf{w}$		

grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.192 A/m

Probe Modulation Factor = 2.53

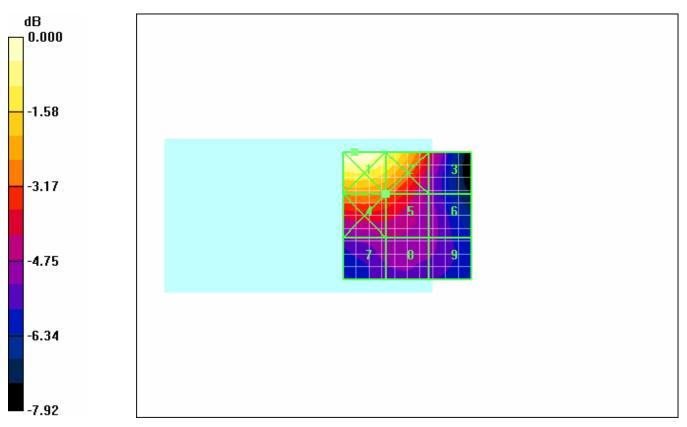
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.066 A/m; Power Drift = -0.146 dB

Peak H-field in A/m

Grid 1	Grid 2	Grid 3
0.269	0.249	0.173
M	M	M
2	3	3
Grid 4	Grid 5	Grid 6
0.202	0.192	0.152
M	\mathbf{M}	\mathbf{M}
3	3	3
Grid 7	Grid 8	Grid 9
0.156	0.156	0.151
\mathbf{M}	\mathbf{M}	M
3	3	3

RTS RIM Testing Services		I Compatibility RF Emissio rry® Smartphone model R		Page 195(216)	
Author Data	Dates of Test	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008 RTS-1191-0809-30 Rev 1 L6ARBW70CW			cw	



0 dB = 0.269 A/m

RTS RIM Testing Services		d Compatibility RF Emission rry® Smartphone model RI		Page 196(216)
Author Data	Dates of Test	Dates of Test Report No FCC ID		
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	CW

Date/Time: 26/08/2008 3:55:49 PM

Test Laboratory: RTS

File Name: HAC_H_CDMA1900_Low_Chan.da4

DUT: BlackBerry Smartphone; Type: Sample ; Serial: Not Specified

Program Name: HAC RF H3DV6 Device

Communication System: CDMA 1900; Frequency: 1851.25 MHz; Duty Cycle: 1:1

Medium parameters used: s = 0 mho/m, $e_r = 1$; density = 1 kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: H3DV6 SN6105; ; Calibrated: 09/11/2007
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 05/03/2008
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.093 A/m; Power Drift = -0.016 dB

Maximum value of Total (measured) = 0.137 A/m

RTS RIM Testing Services	_	d Compatibility RF Emissio rry® Smartphone model R		Page 197(216)	
Author Data	Dates of Test	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008 RTS-1191-0809-30 Rev 1 L6ARBW70CW			cw	

grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.102 A/m

Probe Modulation Factor = 1.00

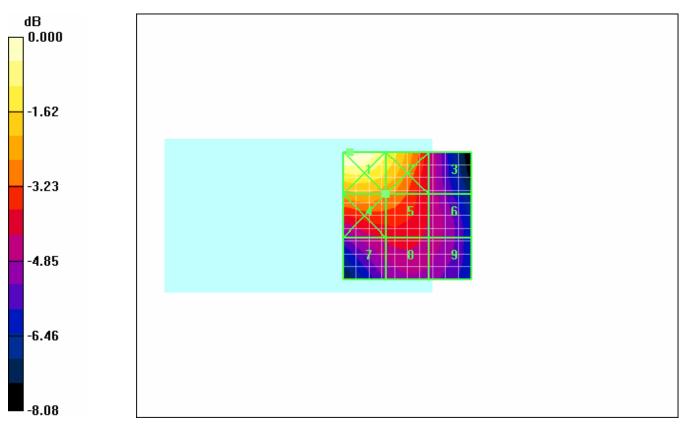
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.093 A/m; Power Drift = -0.016 dB

Peak H-field in A/m

Grid 1	Grid 2	Grid 3
0.137	0.124	0.085
\mathbf{M}	\mathbf{M}	\mathbf{M}
4	4	4
Grid 4	Grid 5	Grid 6
0.106	0.102	0.084
M	M	\mathbf{M}
4	4	4
Grid 7	Grid 8	Grid 9
0.085	0.086	0.082
\mathbf{M}	\mathbf{M}	M
4	4	4

RTS RIM Testing Services		d Compatibility RF Emissio rry® Smartphone model R		Page 198(216)		
Author Data	Dates of Test	Dates of Test Report No FCC ID				
Daoud Attayi	Aug 26, Sep 26-27, 2008 RTS-1191-0809-30 Rev 1 L6ARBW70CW		CW			



0 dB = 0.137 A/m

RTS RIM Testing Services		d Compatibility RF Emission		Page 199(216)	
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Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	cw	

Date/Time: 26/08/2008 4:07:09 PM

Test Laboratory: RTS

File Name: HAC_H_CDMA1900_Mid_Chan.da4

DUT: BlackBerry Smartphone; Type: Sample ; Serial: Not Specified

Program Name: HAC RF H3DV6 Device

Communication System: CDMA 1900; Frequency: 1880 MHz; Duty Cycle: 1:1

Medium parameters used: s = 0 mho/m, $e_r = 1$; density = 1 kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: H3DV6 SN6105; ; Calibrated: 09/11/2007
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 05/03/2008
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.095 A/m; Power Drift = 0.067 dB

Maximum value of Total (measured) = 0.142 A/m

RTS RIM Testing Services		d Compatibility RF Emissio rry® Smartphone model R		Page 200(216)	
Author Data	Dates of Test	es of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008 RTS-1191-0809-30 Rev 1 L6ARBW70CW			\mathbf{cw}	

grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.104 A/m

Probe Modulation Factor = 1.00

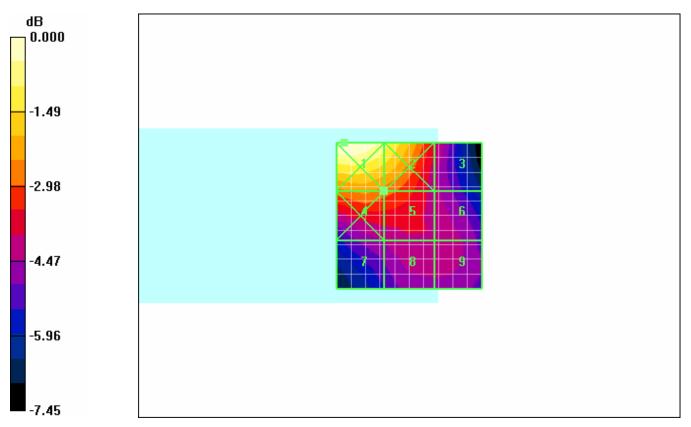
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.095 A/m; Power Drift = 0.067 dB

Peak H-field in A/m

Grid 1	Grid 2	Grid 3
0.142	0.131	0.092
M	\mathbf{M}	\mathbf{M}
4	4	4
Grid 4	Grid 5	Grid 6
0.108	0.104	0.090
M	\mathbf{M}	\mathbf{M}
4	4	4
Grid 7	Grid 8	Grid 9
0.086	0.090	0.089
M	\mathbf{M}	\mathbf{M}
4	4	4

RTS RIM Testing Services		I Compatibility RF Emissio rry® Smartphone model RI		Page 201(216)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70CW	



0 dB = 0.142 A/m

RTS RIM Testing Services	_	I Compatibility RF Emissio rry® Smartphone model R		Page 202(216)	
Author Data	Dates of Test	ates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70CW		

Date/Time: 26/08/2008 4:13:30 PM

Test Laboratory: RTS

File Name: HAC_H_CDMA1900_High_Chan.da4

DUT: BlackBerry Smartphone; Type: Sample; Serial: Not Specified Program Name: HAC RF H3DV6 Device

Communication System: CDMA 1900; Frequency: 1908.5 MHz; Duty Cycle: 1:1

Medium parameters used: s = 0 mho/m, $e_r = 1$; density = 1 kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: H3DV6 SN6105; ; Calibrated: 09/11/2007
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 05/03/2008
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.091 A/m: Power Drift = 0.113 dB

Maximum value of Total (measured) = 0.139 A/m

RTS RIM Testing Services		d Compatibility RF Emissio rry® Smartphone model R		Page 203(216)	
Author Data	Dates of Test	es of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008 RTS-1191-0809-30 Rev 1 L6ARBW70CW			\mathbf{cw}	

grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.101 A/m

Probe Modulation Factor = 1.00

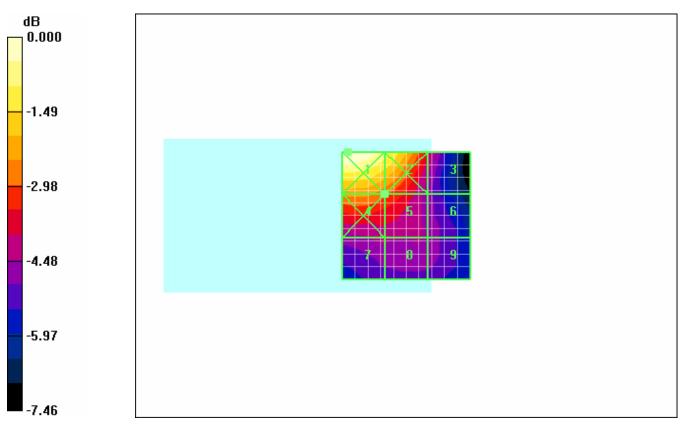
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.091 A/m; Power Drift = 0.113 dB

Peak H-field in A/m

Grid 1	Grid 2	Grid 3
0.140	0.129	0.091
\mathbf{M}	M	\mathbf{M}
4	4	4
Grid 4	Grid 5	Grid 6
0.107	0.101	0.083
\mathbf{M}	\mathbf{M}	\mathbf{M}
4	4	4
Grid 7	Grid 8	Grid 9
0.085	0.085	0.083
M	\mathbf{M}	${f M}$
4	4	4

RTS RIM Testing Services		d Compatibility RF Emission rry® Smartphone model R		Page 204(216)	
Author Data	Dates of Test	ates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70CW		



0 dB = 0.140 A/m

RTS RIM Testing Services	_	I Compatibility RF Emissio rry® Smartphone model R		Page 205(216)	
Author Data	Dates of Test	tes of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70CW		

Date/Time: 25/06/2008 10:44:08 AM

Test Laboratory: RTS

File Name: HAC_E_Ambient Noise_835MHz.da4

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: Not Specified

Program Name: HAC RF E Dipole

Communication System: CW; Frequency: 835 MHz; Duty Cycle: 1:1 Medium parameters used: s = 0 mho/m, $e_r = 1$; density = 1000 kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: ER3DV6 SN2286; ConvF(1, 1, 1); Calibrated: 21/01/2008
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 05/03/2008
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x37x1):

Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.000 V/m; Power Drift = 999.0 dB

Maximum value of Total (measured) = 1.68 V/m

E Scan - measurement distance from the probe sensor center to

RTS RIM Testing Services	_	d Compatibility RF Emissio rry® Smartphone model R		Page 206(216)	
Author Data	Dates of Test	rates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008 RTS-1191-0809-30 Rev 1 L6ARBW70CW			$\mathbf{c}\mathbf{w}$	

CD835 Dipole = 10mm/Hearing Aid Compatibility Test

(41x361x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 1.68 V/m

Probe Modulation Factor = 1.00

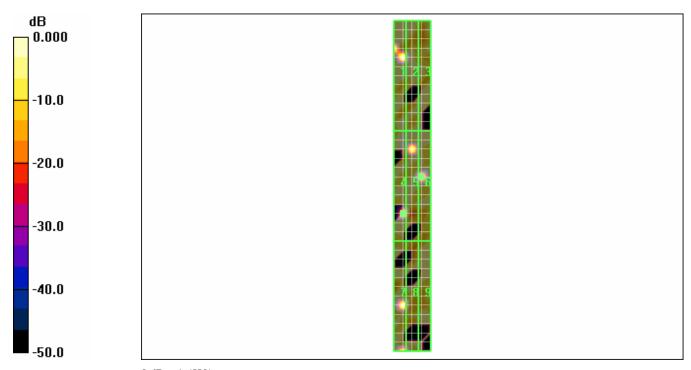
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.000 V/m; Power Drift = 999.0 dB

Peak E-field in V/m

Grid 1	Grid 2	Grid 3
1.57	0.408	0.000
M	M	M
4	4	4
Grid 4	Grid 5	Grid 6
1.59	1.18	1.68
M	M	M
4	4	4
Grid 7	Grid 8	Grid 9
1.50	0.596	0.000
M	M	M
4	4	4

RTS RIM Testing Services		d Compatibility RF Emissio rry® Smartphone model R		Page 207(216)	
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Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70CW		



 $0\ dB=1.68V/m$

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Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70CW	

Date/Time: 25/06/2008 11:01:47 AM

Test Laboratory: RTS

File Name: HAC_E_Ambient Noise_1880MHz.da4

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: Not Specified

Program Name: HAC RF E Dipole

Communication System: CW; Frequency: 835 MHz; Duty Cycle: 1:1 Medium parameters used: s = 0 mho/m, $e_r = 1$; density = 1000 kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: ER3DV6 SN2286; ConvF(1, 1, 1); Calibrated: 21/01/2008
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 05/03/2008
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x37x1):

Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.658 V/m; Power Drift = -0.581 dB

Maximum value of Total (measured) = 1.69 V/m

E Scan - measurement distance from the probe sensor center to

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Author Data	Dates of Test	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	191-0809-30 Rev 1 L6ARBW70CW		

CD835 Dipole = 10mm/Hearing Aid Compatibility Test

(41x361x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 1.69 V/m

Probe Modulation Factor = 1.00

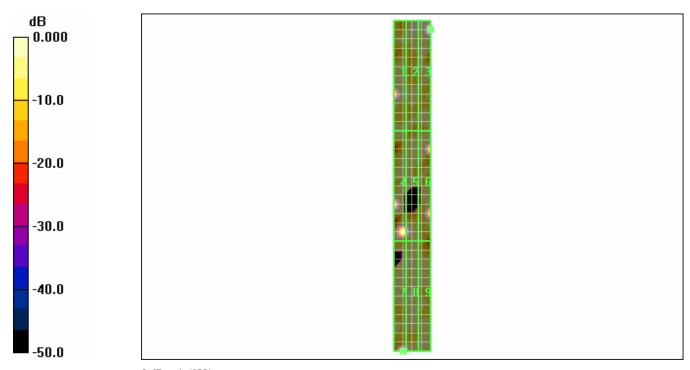
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.658 V/m; Power Drift = -0.581 dB

Peak E-field in V/m

Grid 1	Grid 2	Grid 3
1.09	0.000	1.60
M	${f M}$	M
4	4	4
Grid 4	Grid 5	Grid 6
1.55	0.470	1.14
M	M	M
4	4	4
Grid 7	Grid 8	Grid 9
1.69	0.696	0.000
M	\mathbf{M}	M
4	4	4

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Author Data	Dates of Test Report No FCC ID			
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 $0\ dB=1.69V/m$

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Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70C	CW

Date/Time: 25/06/2008 2:32:22 PM

Test Laboratory: RTS

File Name: HAC_H_Ambient Noise_835MHz.da4

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: Not Specified

Program Name: HAC RF H3DV6 Dipole

Communication System: CW; Frequency: 835 MHz; Duty Cycle: 1:1 Medium parameters used: s = 0 mho/m, $e_r = 1$; density = 1 kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: H3DV6 SN6105; ; Calibrated: 09/11/2007
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 05/03/2008
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x37x1):

Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm Reference Value = 0.003 A/m; Power Drift = 1.02 dB

Maximum value of Total (measured) = 0.007 A/m

H Scan - measurement distance from the probe sensor center to

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Author Data	Dates of Test	Dates of Test Report No FCC ID			
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CD835 Dipole = 10mm/Hearing Aid Compatibility Test

(41x361x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.007 A/m

Probe Modulation Factor = 1.00

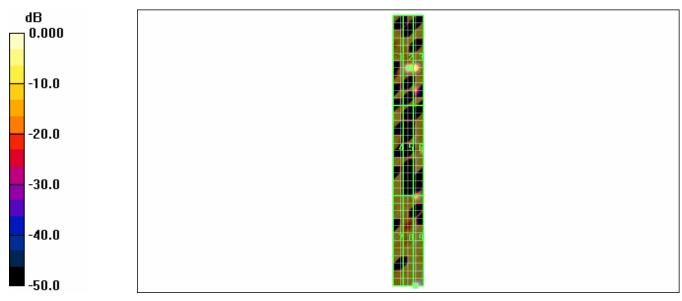
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.003 A/m; Power Drift = 1.02 dB

Peak H-field in A/m

Grid 1 0.000	Grid 2 0.006	Grid 3 0.005
0.000 M	0.000 M	0.005 M
4	4	4
Grid 4	Grid 5	Grid 6
0.000	0.001	0.002
\mathbf{M}	\mathbf{M}	\mathbf{M}
4	4	4
Grid 7	Grid 8	Grid 9
0.000	0.003	0.007
M	\mathbf{M}	M
4	4	4

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RIM Testing Services		213(210)		
Author Data	Dates of Test Report No FCC ID			
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 $0\ dB=0.007A/m$

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Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	Aug 26, Sep 26-27, 2008	RTS-1191-0809-30 Rev 1	L6ARBW70CW	

Date/Time: 25/06/2008 2:41:50 PM

Test Laboratory: RTS

File Name: HAC_H_Ambient Noise_1880MHz.da4

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: Not Specified

Program Name: HAC RF H3DV6 Dipole

Communication System: CW; Frequency: 1880 MHz; Duty Cycle: 1:1 Medium parameters used: s = 0 mho/m, $e_r = 1$; density = 1 kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 09/11/2007

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 05/03/2008

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8

Build 184

H Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x37x1):

Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.001 A/m; Power Drift = 2.15 dB

Maximum value of Total (measured) = 0.003 A/m

H Scan - measurement distance from the probe sensor center to

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CD835 Dipole = 10mm/Hearing Aid Compatibility Test

(41x361x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.004 A/m

Probe Modulation Factor = 1.00

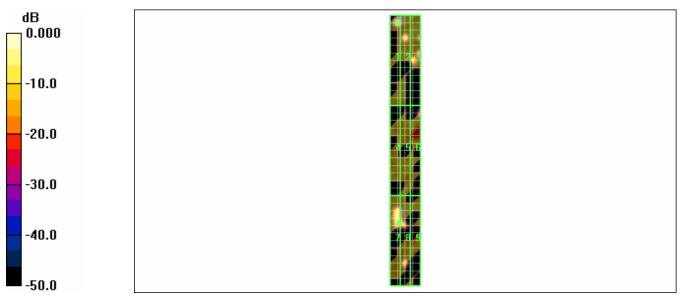
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.001 A/m; Power Drift = 2.15 dB

Peak H-field in A/m

Grid 2 0.002	Grid 3 0.002
M 4	M 4
Grid 5 0.000	Grid 6 0.002
M 4	M 4
Grid 8	Grid 9
0.003	0.000
M	M
	0.002 M 4 Grid 5 0.000 M 4 Grid 8 0.003

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 $0\;dB=0.004A/m$